

TEMPUS Detector: Recent Developments and Applications

DESY FS-DS

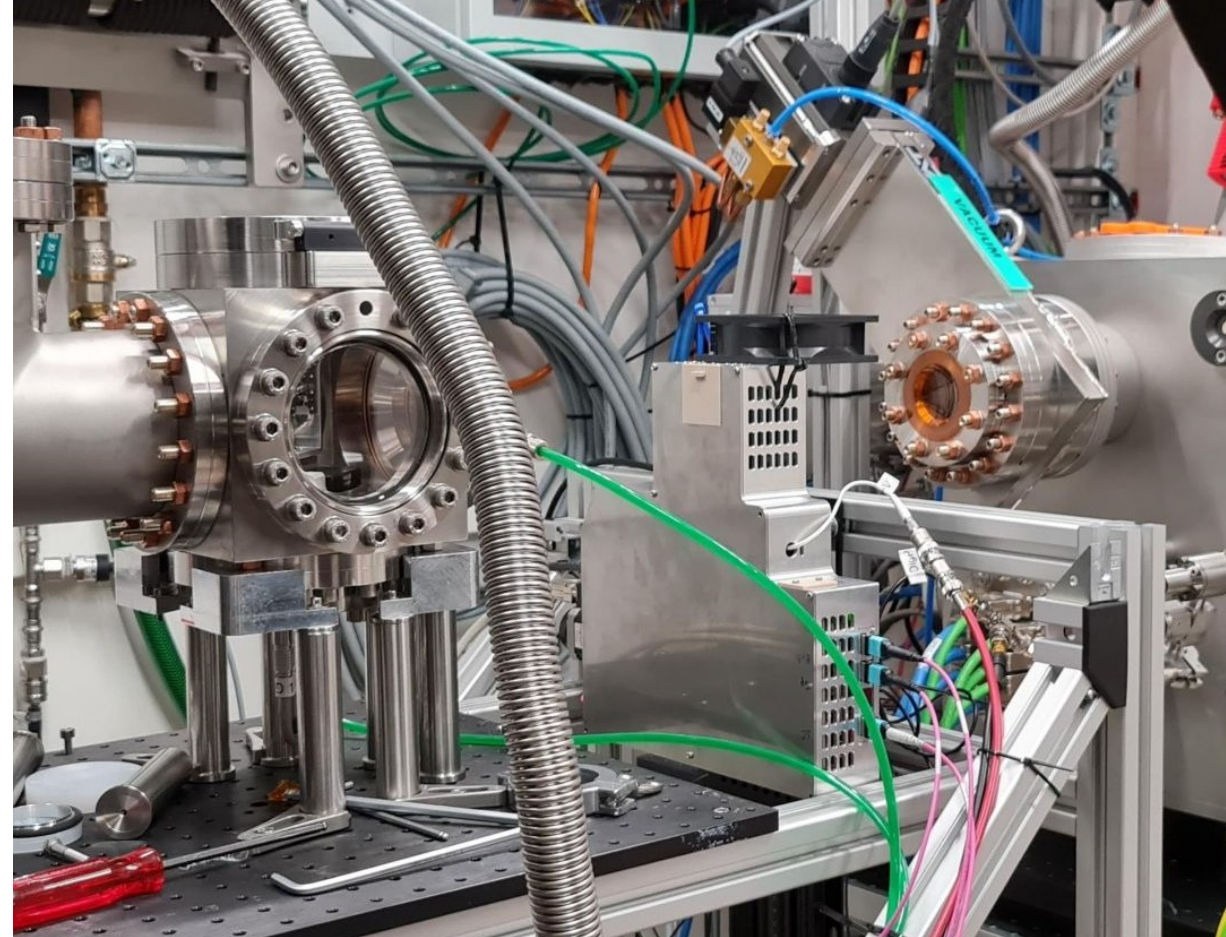
Photon Science Detector Group

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S. Fridman, S. Lange, H. Graafsma

The TEMPUS X-ray Detector System

Goal & Concept

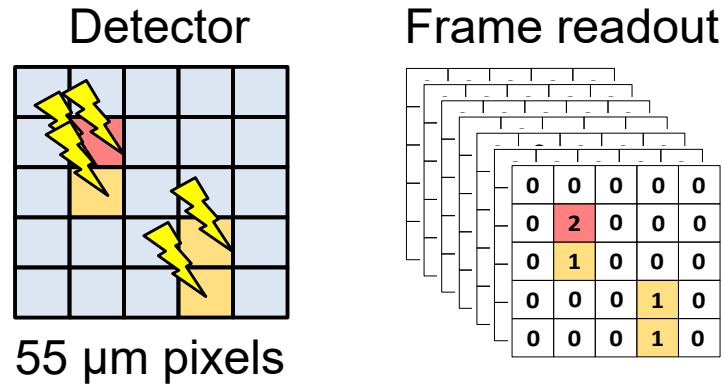
- Detector system developed at DESY for time-resolved X-ray science
- Detector upgrade for PETRA-III and PETRA-IV, also suitable for other x-ray beamlines
- Hybrid pixel detector system, based on Timepix4:
 - Single chip 2.8 x 2.5 cm
 - 55 μm pixel pitch
 - Combines improved characteristics from Medipix3 and Timepix3
 - Provides sub-nanosecond timing and energy measurements



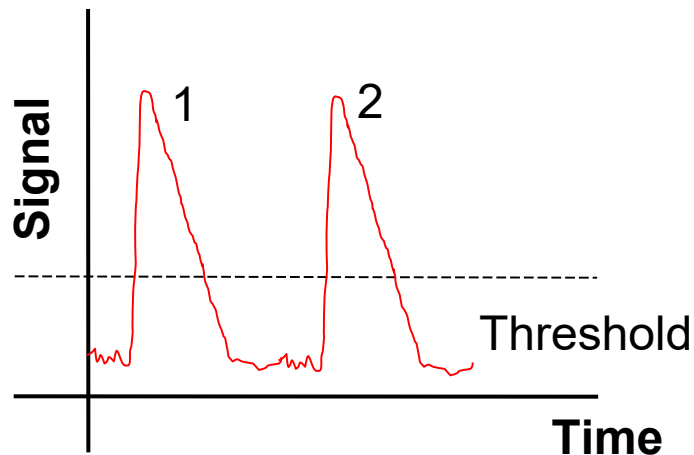
The Timepix4 Readout Chip

Operation modes

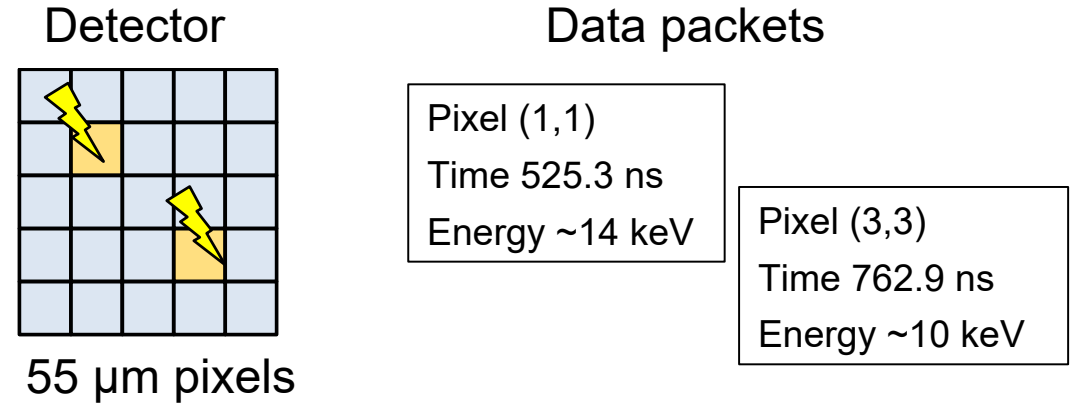
1) Photon counting and frame readout



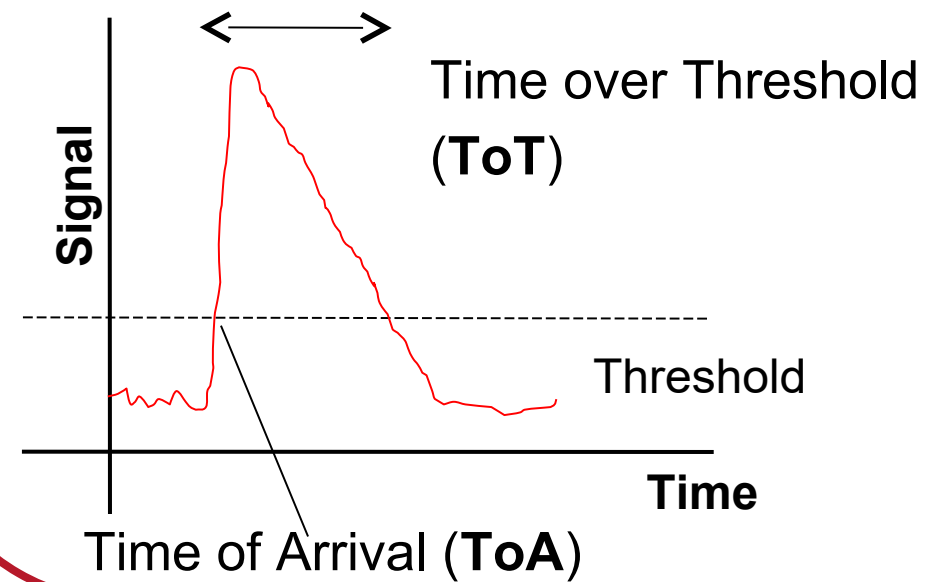
- 40 kHz frame rate CRW (8 bits)
- $\sim 1.5 \times 10^6$ counts/pixel/s



2) Time-stamping and event-driven readout



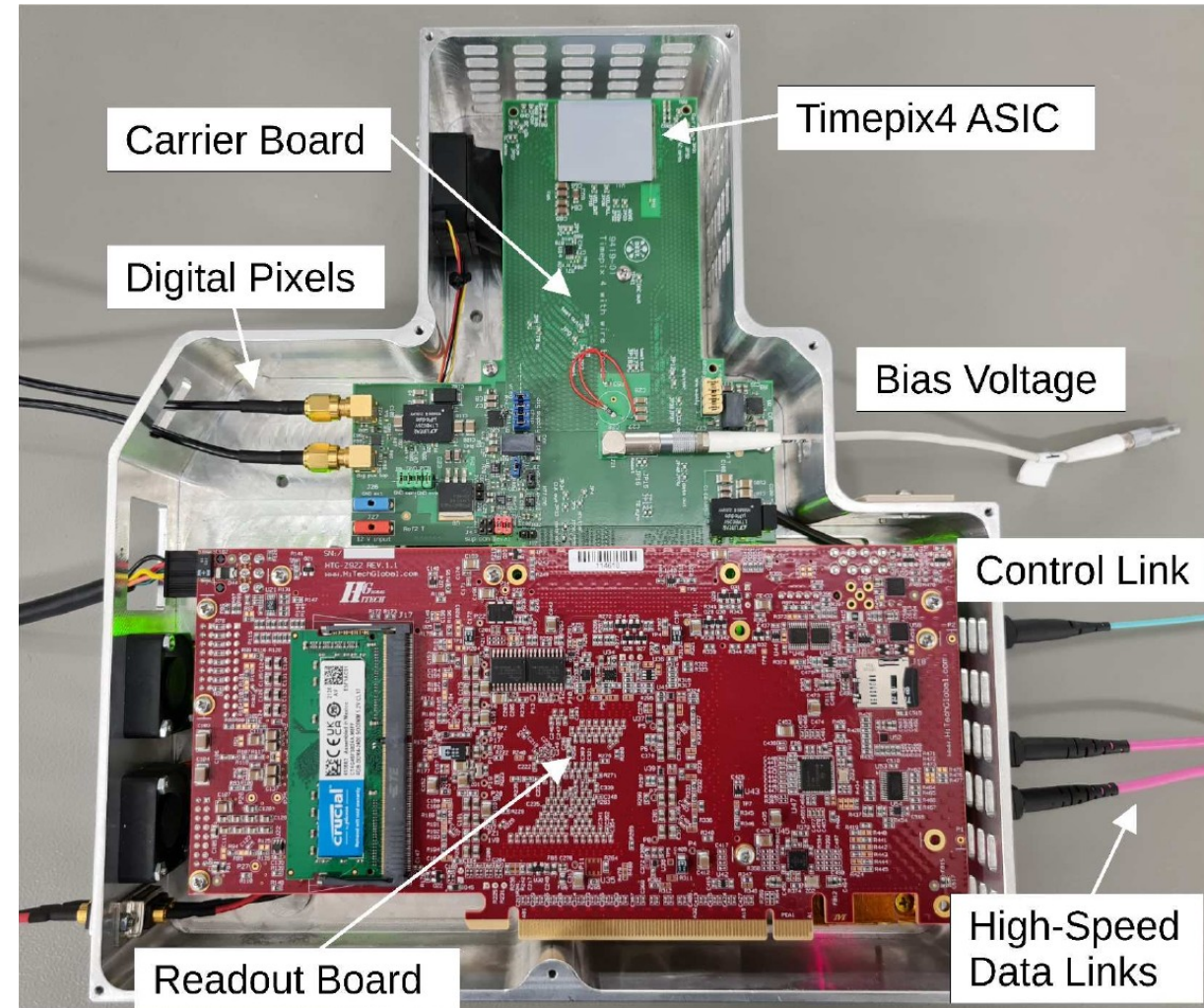
- X-rays $\sim$ ns time resolution
- $\sim 1 \times 10^9$ counts/chip/s



Latest Developments

Current status and on-going work

- Improve cooling with Peltier element
- Better stability of parallel readout with GWT links:
 - 2 links running at 2.56 Gbps
 - 16 links running at 1.28 Gbps
- Improvements in control software
- Configuring test pulses for energy calibration
- Clustering algorithm
- Data saving using Rust
 - Limitations at very high rates (e.g. 16-link readout)



J. Correa et al. (2024). *J. Synchrotron Rad.* **31**. <https://doi.org/10.1107/S1600577524005319>

Latest Developments

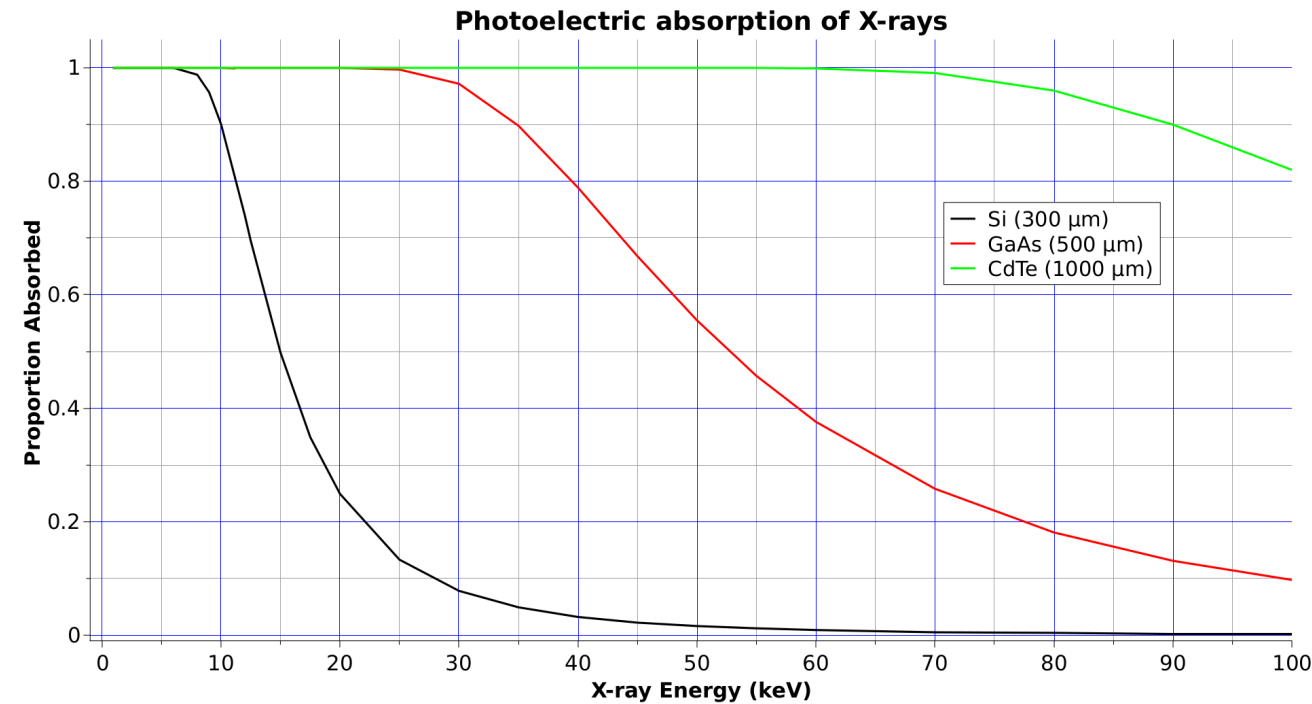
Available Systems

> Silicon Sensors (hole-collecting)

- 500 μm thick $\rightarrow$ increased probability of interaction
- 300 μm thick $\rightarrow$ better timing
- 300 μm thick with a thin entrance window (TEW) $\rightarrow$ visible light

> CdTe Sensor (electron-collecting)

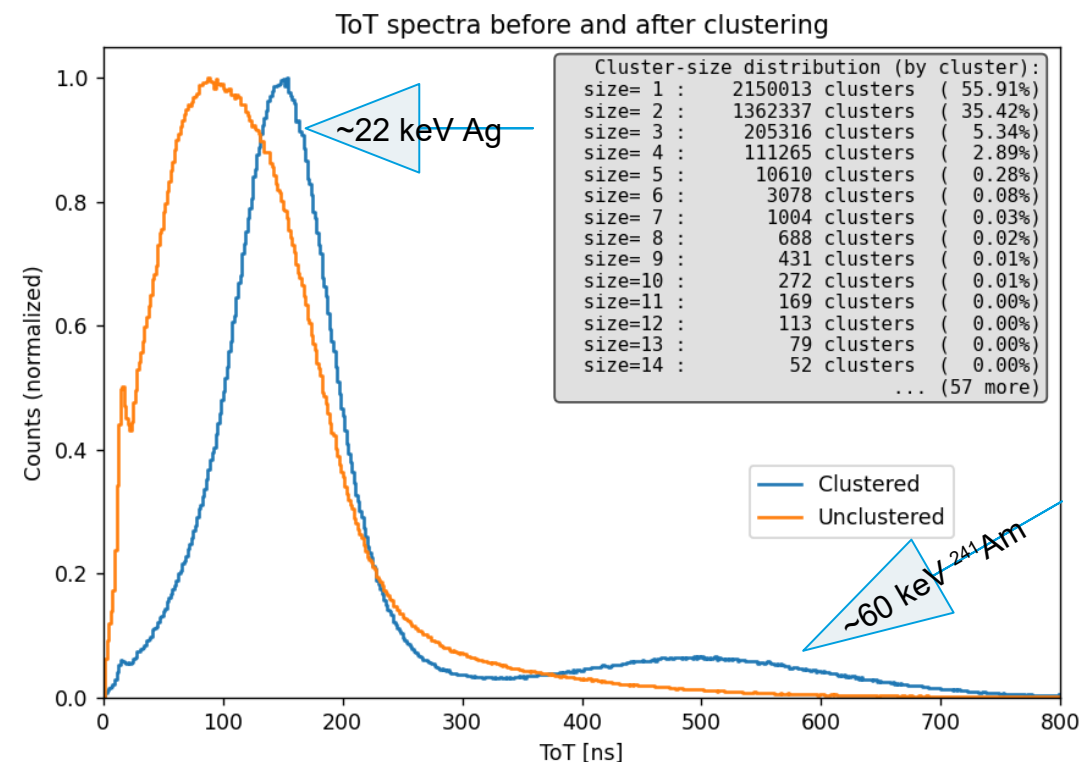
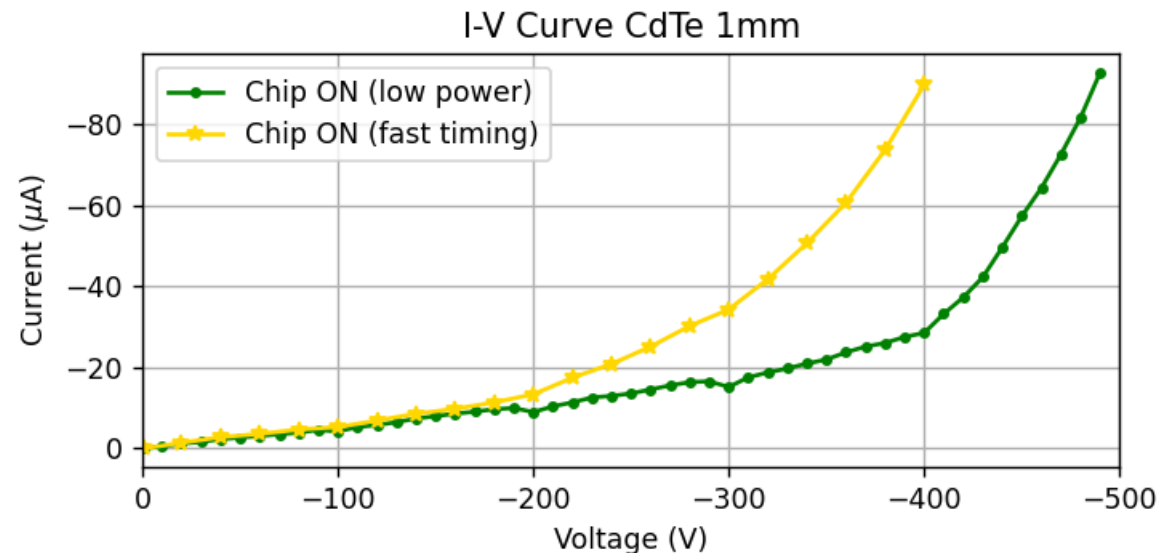
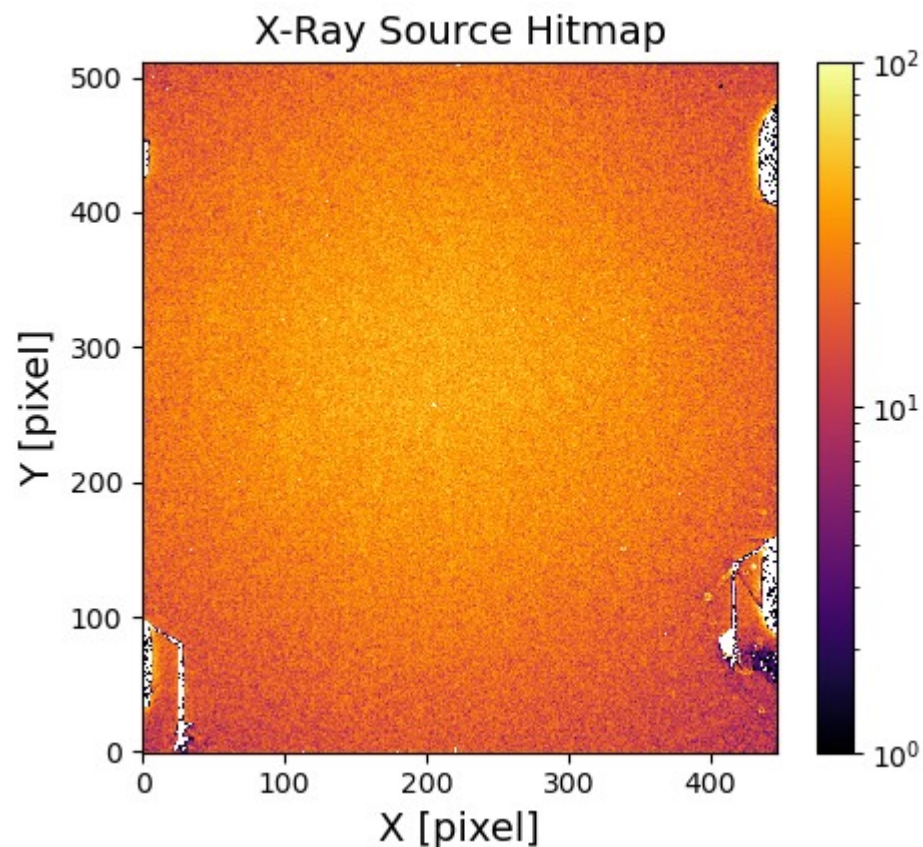
- 1 mm thick
 - $\rightarrow$ Larger energy range interaction
 - $\rightarrow$ More localized X-ray absorption, improving consistency of drift time



Latest Developments

CdTe System

- Leakage current dependent on configuration
- Hitmap → “disconnected” pixels
- Detectable 60 keV peak from ^{241}Am source



Latest User Experiment

Nuclear Resonance Scattering

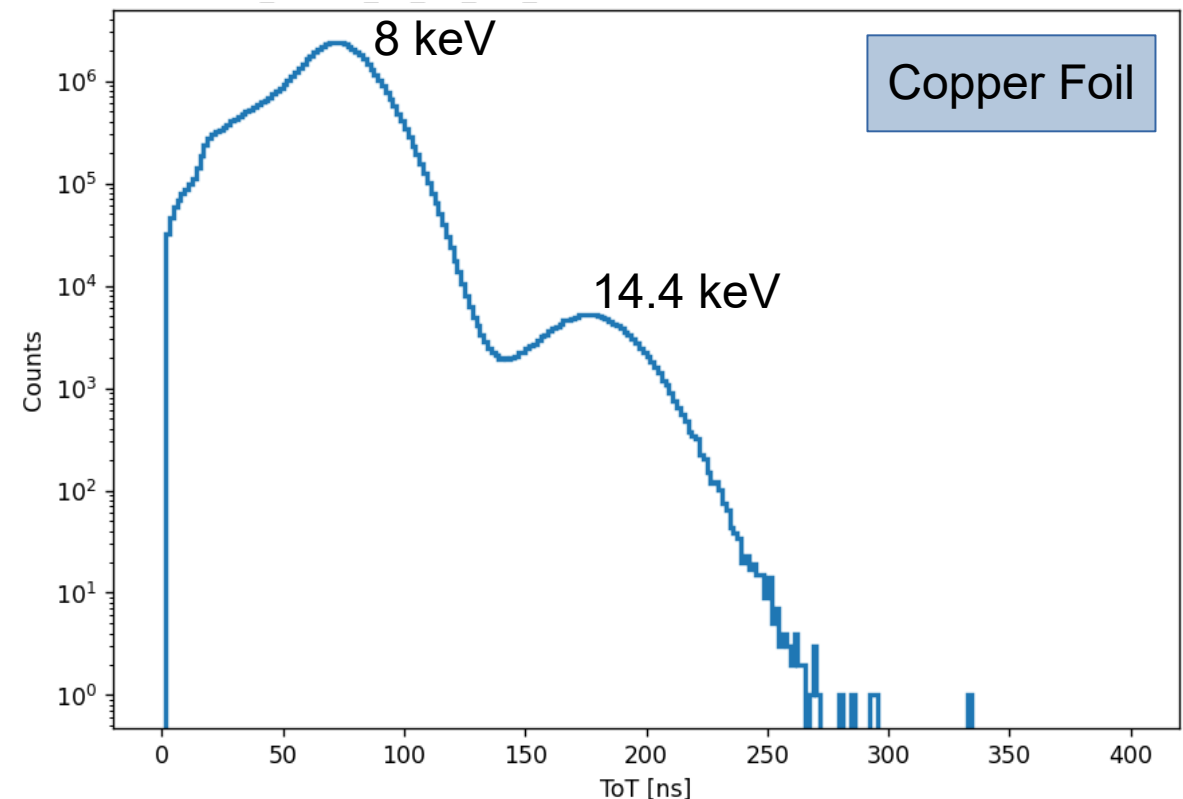
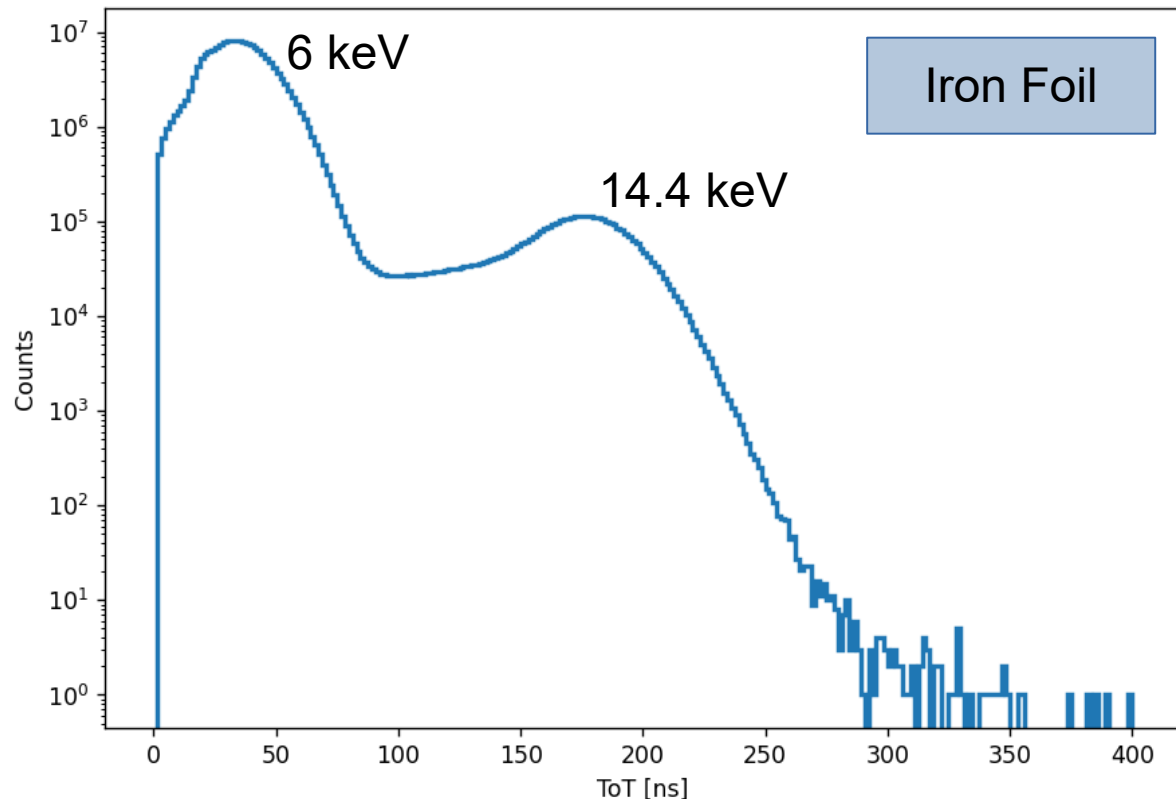
- Latest campaign at P01 in August 2025
- Probe internal structure of atomic nuclei by using resonant absorption and **re-emission of photons**
- X-ray beam: **14.4 keV**
- Samples: iron (**~ 6 keV**) and copper (**~ 8 keV**) foils
- All tests done in incoherent geometry (90 deg to incident beam)
- Two different detectors:
 - 1mm CdTe sensor @ -250 V bias
 - 300 um Si sensor TEW @ 200 V bias
- Time of arrival (ToA) relative to bunch trigger / revolution clock
- **Goal: measure time-delayed photons from nuclear excitation**



Nuclear Resonance Scattering – Preliminary Results

Time-over-threshold (ToT) Measurements

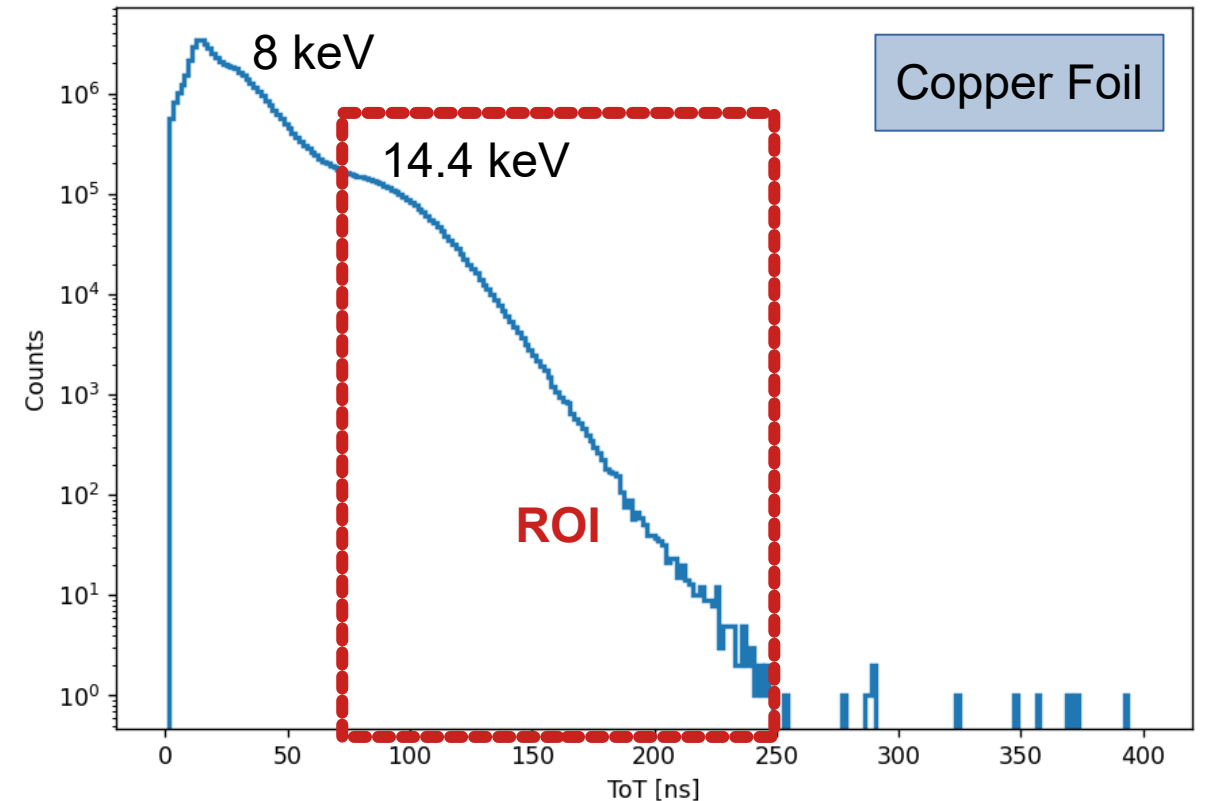
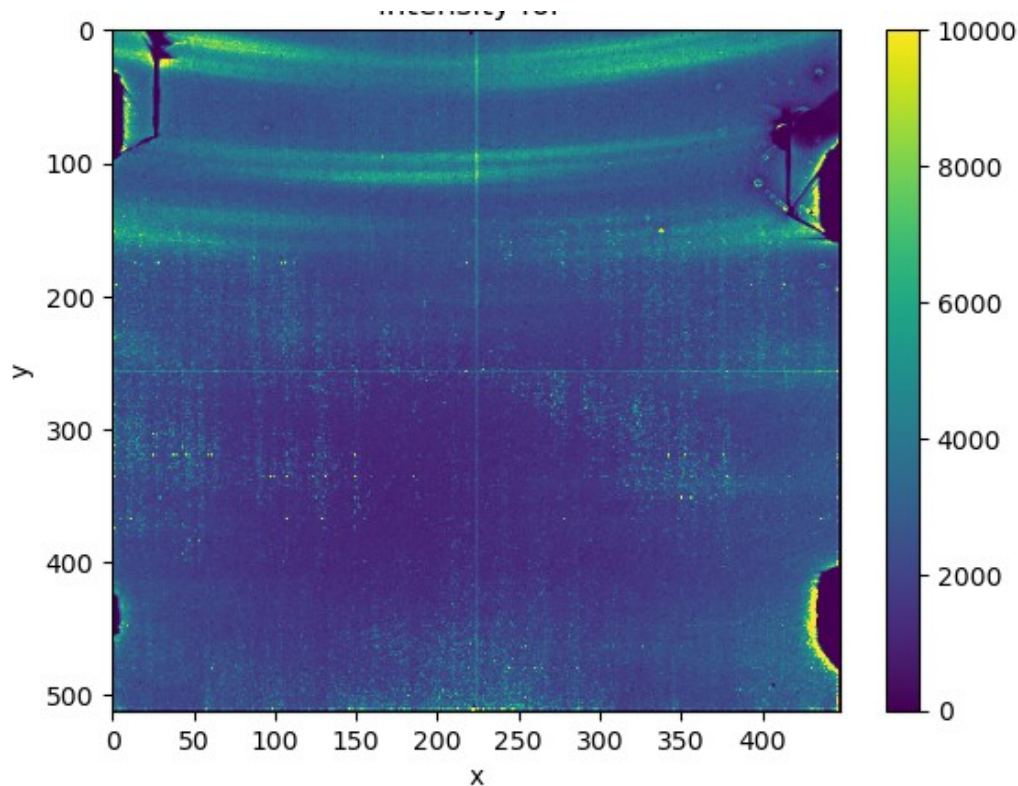
- **Si 300 μm TEW**
- Photopeaks from main beam and from target foil are well distinguished
- No energy calibration yet



Nuclear Resonance Scattering – Preliminary Results

Time-over-threshold (ToT) Measurements

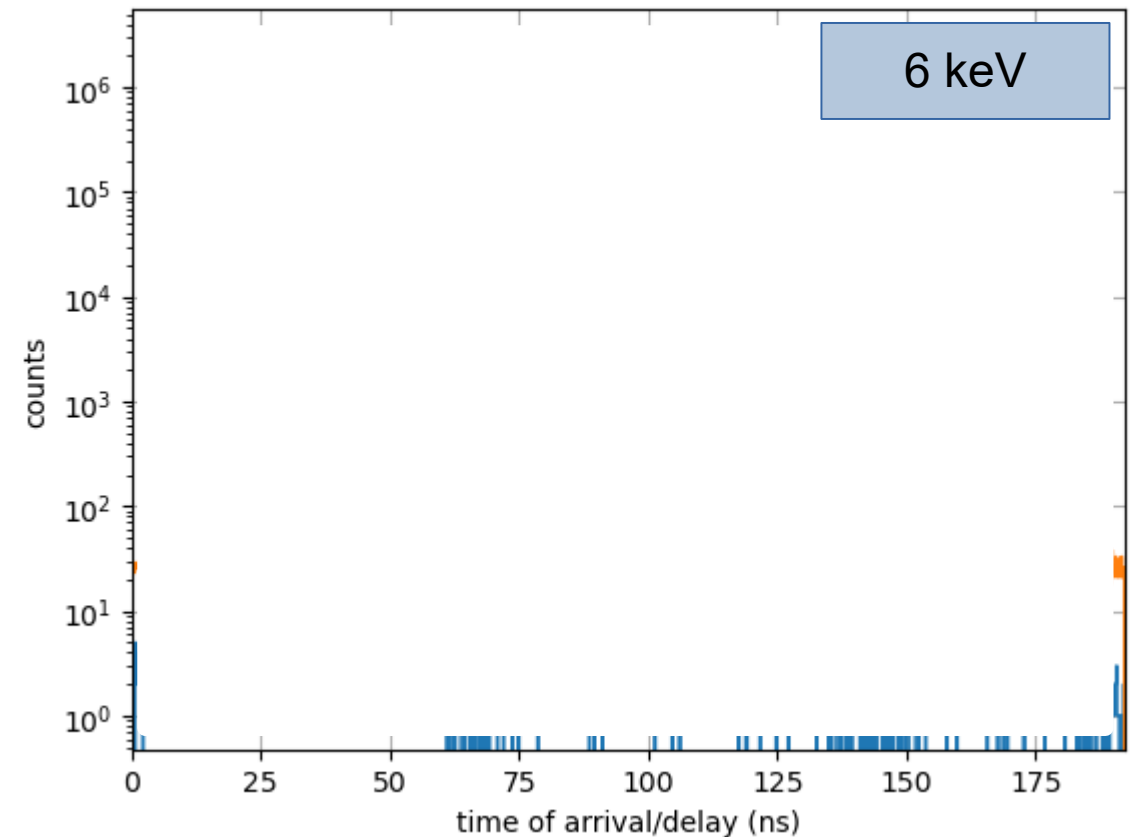
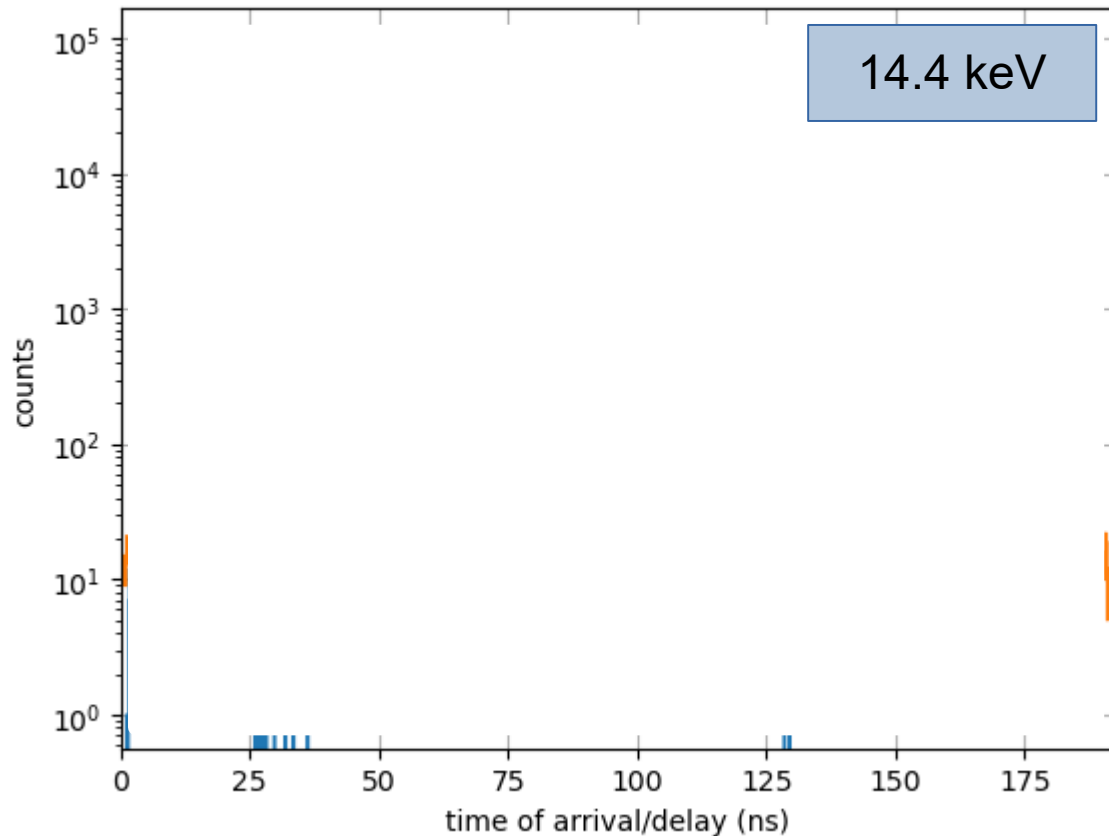
- **CdTe 1mm**
- The 2 photopeaks (from main beam and from copper foil) are difficult to distinguish
- Clustering does not improve the spectrum → likely too high threshold



Nuclear Resonance Scattering – Preliminary Results

Time-of-arrival (ToA) Measurements

- **Si 300 um TEW**, iron foil
- ROI to select photopeaks
- Resonance **OFF** and **ON** (delayed photons)

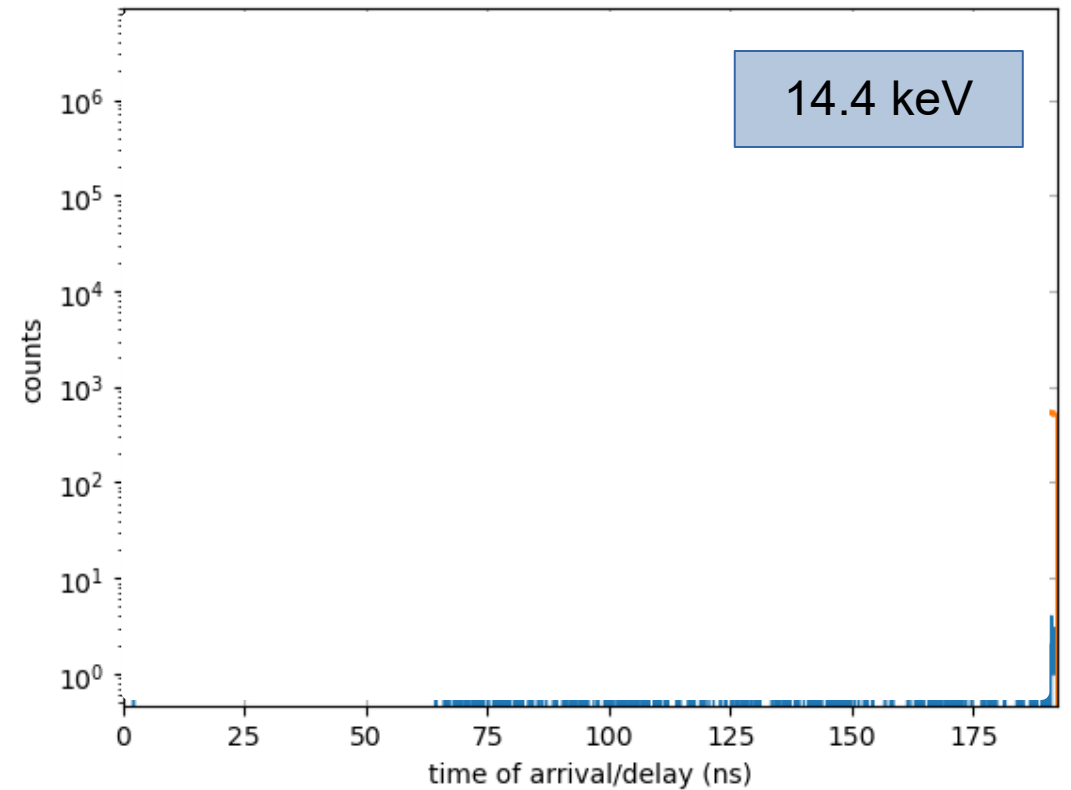
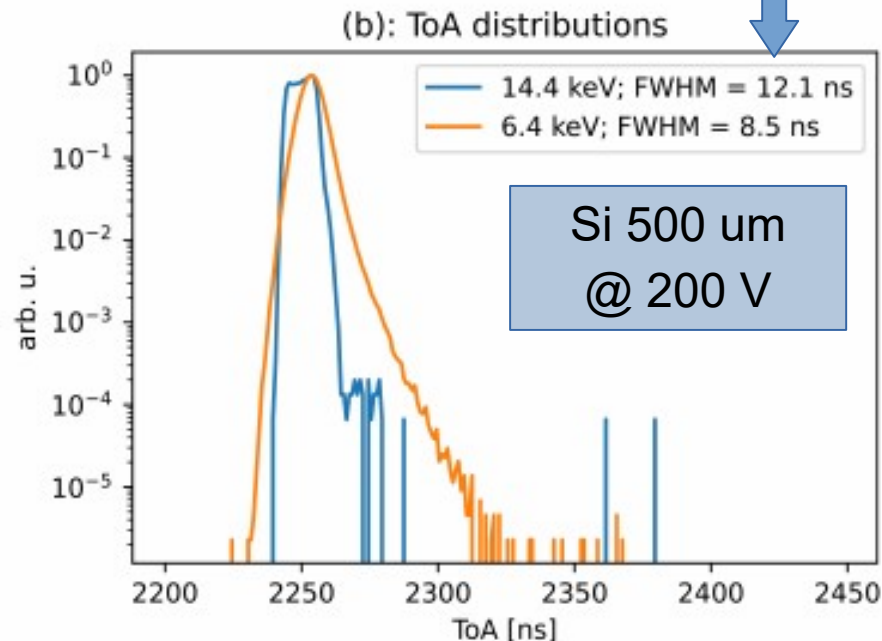


Nuclear Resonance Scattering – Preliminary Results

Time-of-arrival (ToA) Measurements

- **CdTe 1 mm**
- Resonance **OFF** and **ON** (delayed photons)
- No calibration or clustering yet

Almost 2x better timing!



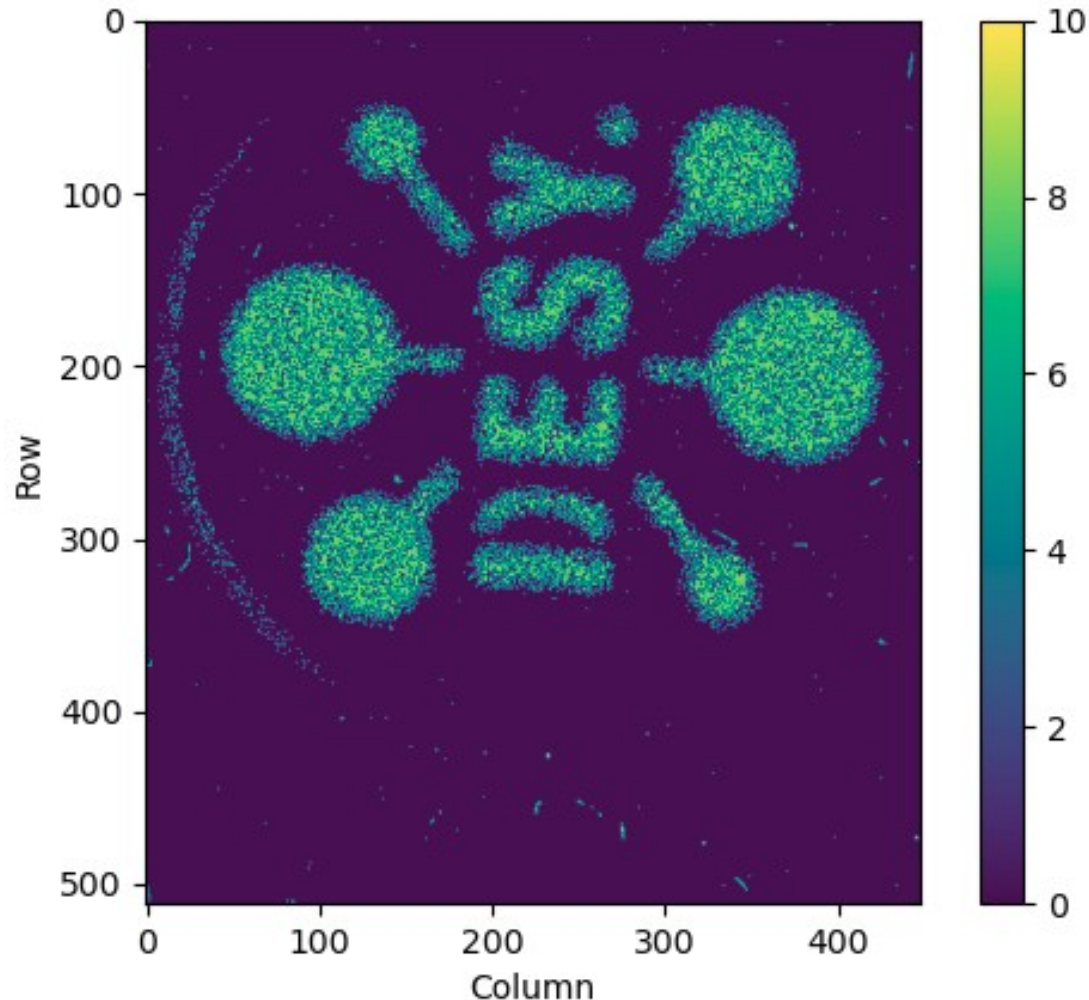
The TEMPUS X-ray detector

Summary / Outlook

- A **single-chip Timepix4-based prototype** is being developed by DESY
 - Reach the **limits of the chip** and **introduce the event-driven** readout in photon-science
 - Different systems available
 - Achieved **O(~ns)** timing resolution
- Applications with strong interest in this system: **NRS**, XPCS, Parametric Down Conversion, AMO...
- Next steps:
 - 3 Beamtimes at ESRF in November
 - Energy and time calibration
 - Use of **alternative sensors** such as **high-Z** materials and **LGADs**:
 - **Expand the photon energy range** of current system
 - Overcome the silicon sensor **time resolution** limitations for X-rays

Acknowledgments

Collaborators



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Marco Cammarata
Rudolf Rueffer

Backup Slides

TEMPUS

The Timepix4 readout chip

Comparison with Timepix3

			Timepix3 (2013)	Timepix4 (2019/20)	
Technology			IBM 130 nm – 8 metal	TSMC 65 nm – 10 metal	
Pixel size			55 x 55 μm	55 x 55 μm	
Pixel arrangement			3-side buttable 256 x 256	4-side buttable (TSV) 512 x 448	3.5 x
Sensitive area			1.98 cm ²	6.94 cm ²	
Readout modes	Data driven (tracking)	Mode	ToT and TOA		
		Event packet	48-bit	64-bit	
		Max rate	< 43 Mhits/cm ² /s	357.6 Mhits/cm ² /s	8 x
		Pix rate equiv.	1.3 kHz/pix average	10.8 kHz/pix average	
	Frame Based (imaging)	Mode	Count: 10 bit + iToT	Count: 8 or 16 bit CRW	
		Frame	Zero suppressed (with pix addr)	Full frame (no pix addr)	
		Max count rate	82 Ghits/cm ² /s	~ 800 Ghits/cm ² /s	10 x
		Max frame rate	N/A (worst case: 0.8ms readout)	80 kHz CRW	
TOT energy resolution			< 2 keV	< 1 keV	2 x
Time resolution			1.56 ns	~ 200 ps	8 x
Readout bandwidth			≤ 5.12 Gbps (8 x 640 Mbps)	≤163.8 Gbps (16 x 10.2 Gbps)	32 x
Target minimum threshold			< 500 e ⁻	< 500 e ⁻	

Some comments on the time resolution

Time jitter

TOA resolution

Signal for
12 keV
photon
↓

- > **Variation in timing due to noise or variability in instant signal**, this depends on peaking time of amplifier response

Timepix4 ASIC time resolution; measured by CERN with internal test pulses

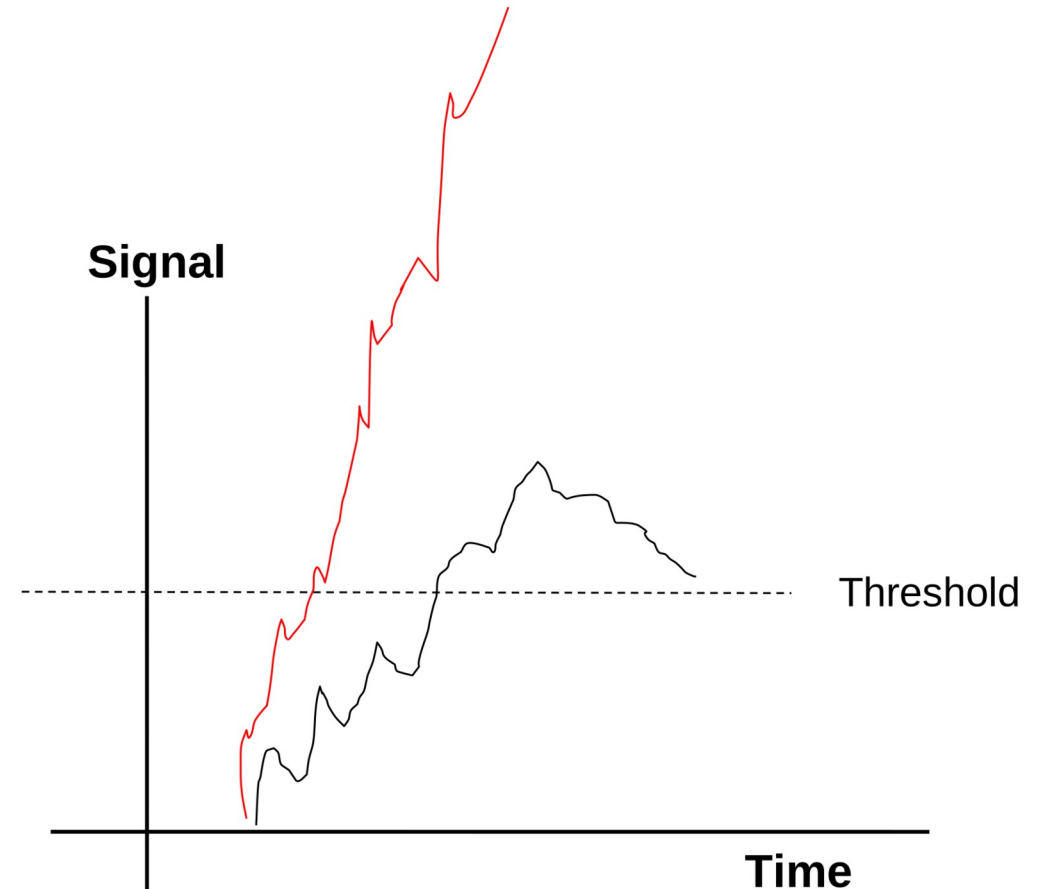
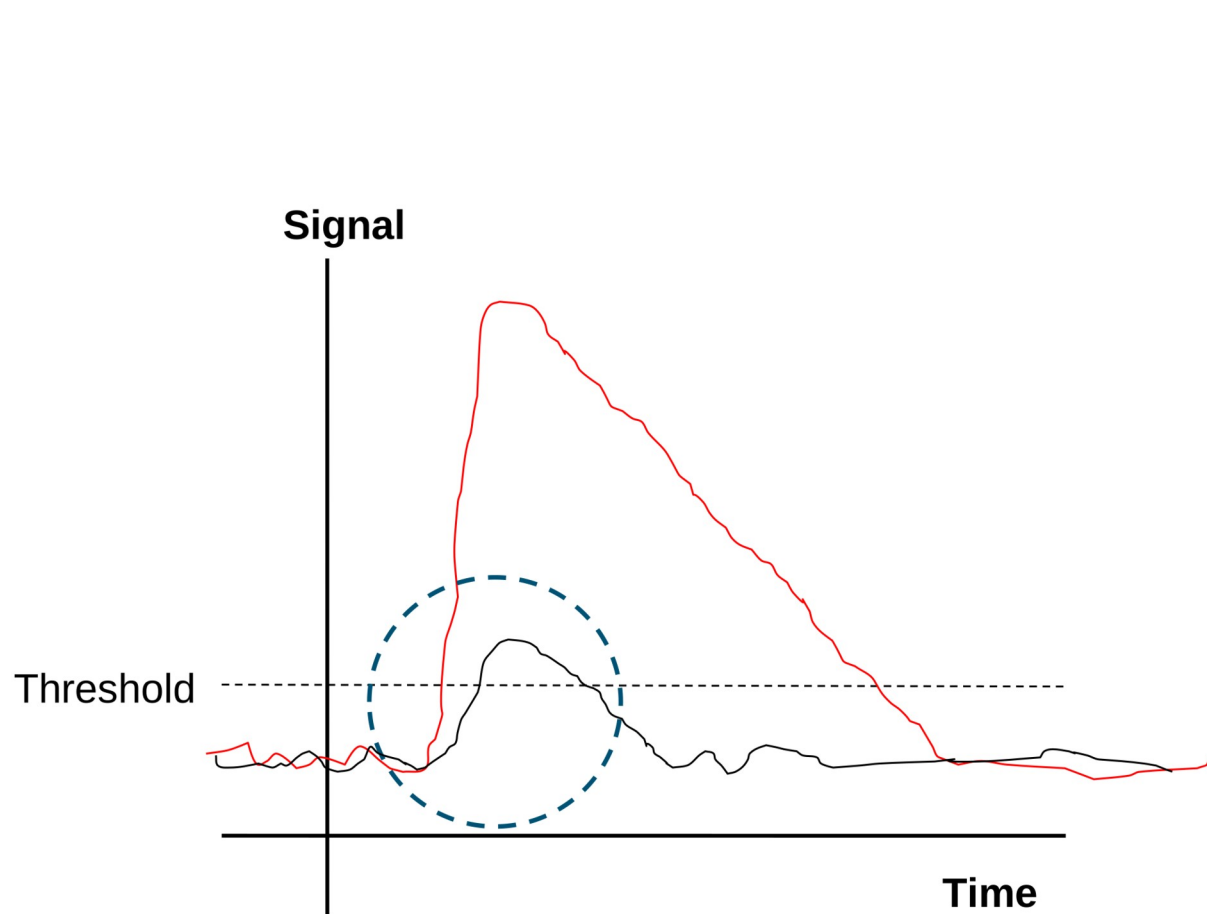
Note; in Si, 3.6 keV energy generates 1000 e-h pairs

~0.7 ns FWHM for 12 keV photons

Some comments on time resolution

Timewalk

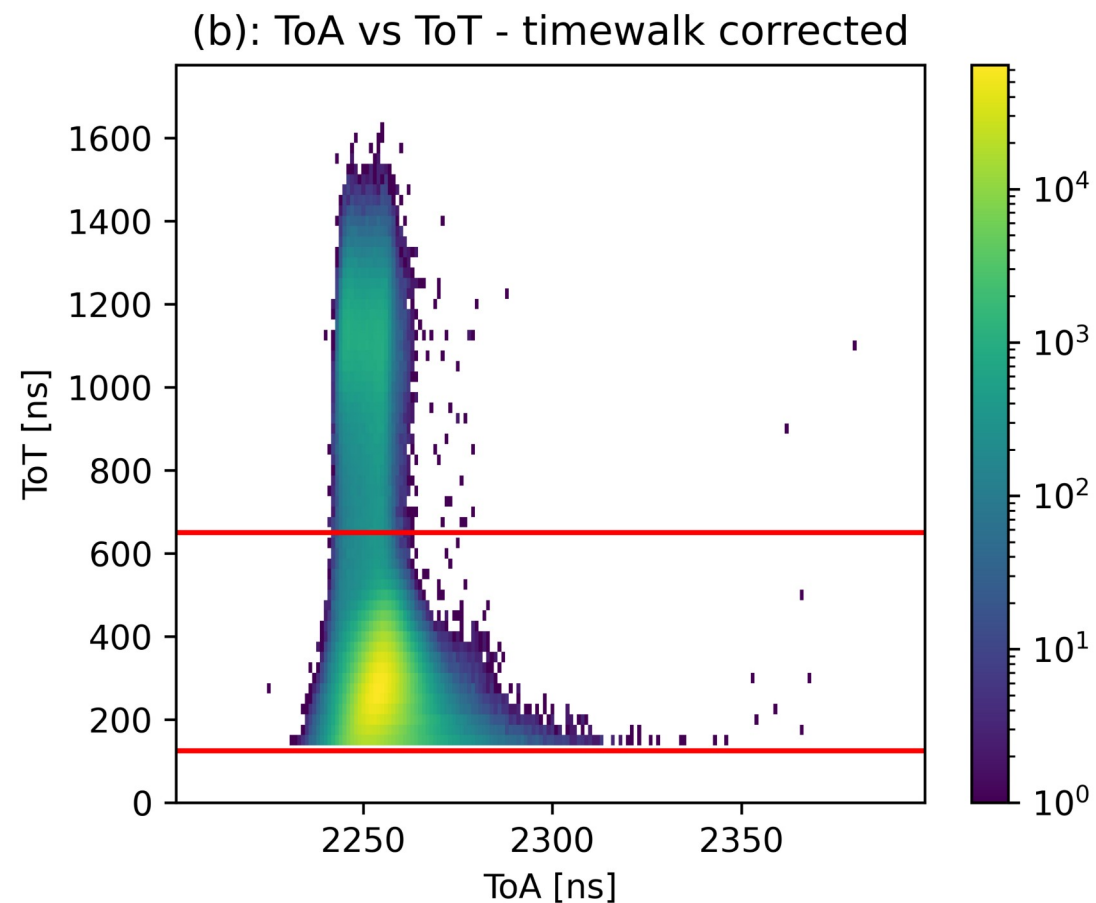
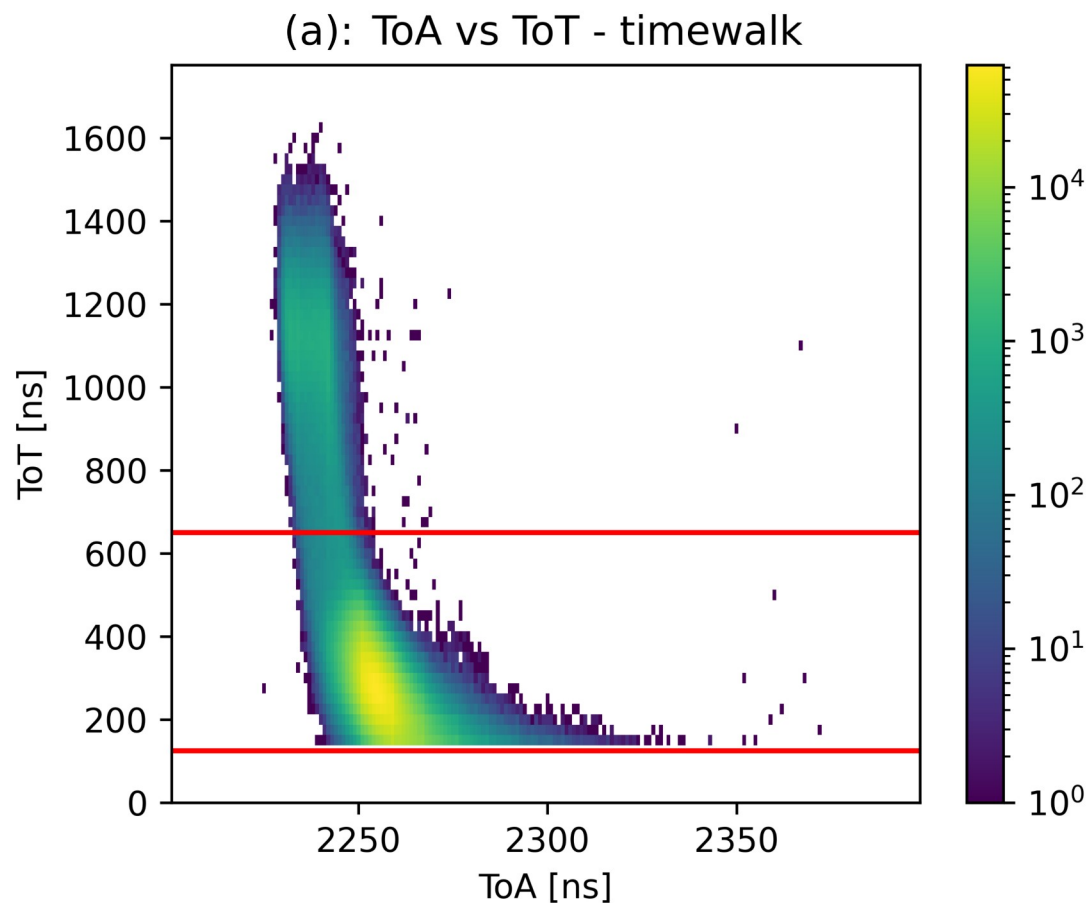
- Time delay before signal reaches threshold
 - Assuming instant signal, this depends on peaking time of amplifier response



Some comments on the time resolution

First Experiments @ ESRF

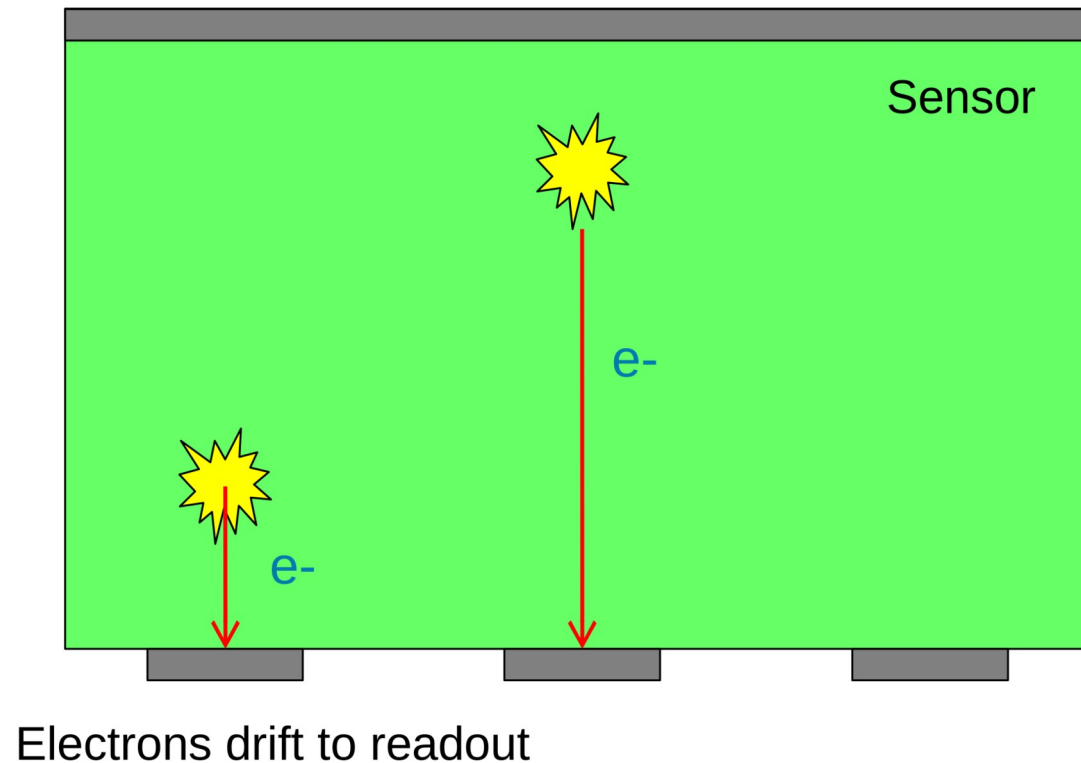
- Time-walk correction
 - Helped to improved the time resolution obtained



Some comments on the time resolution

Signal speed

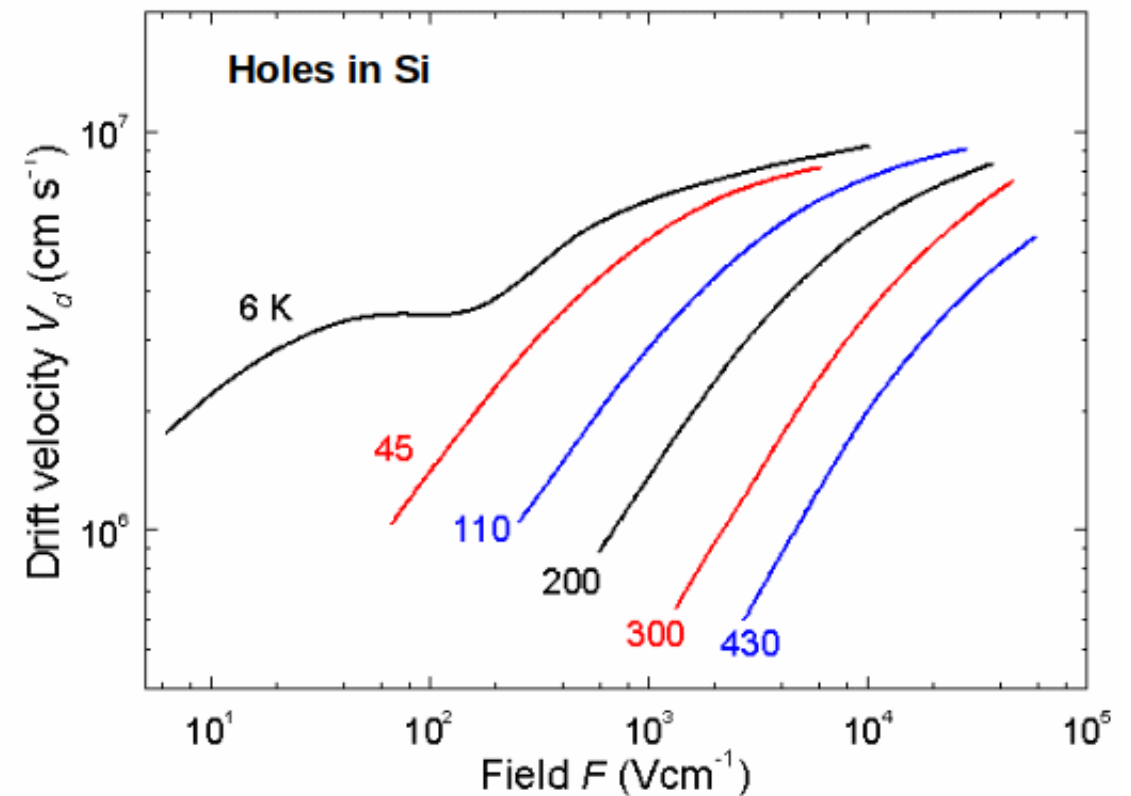
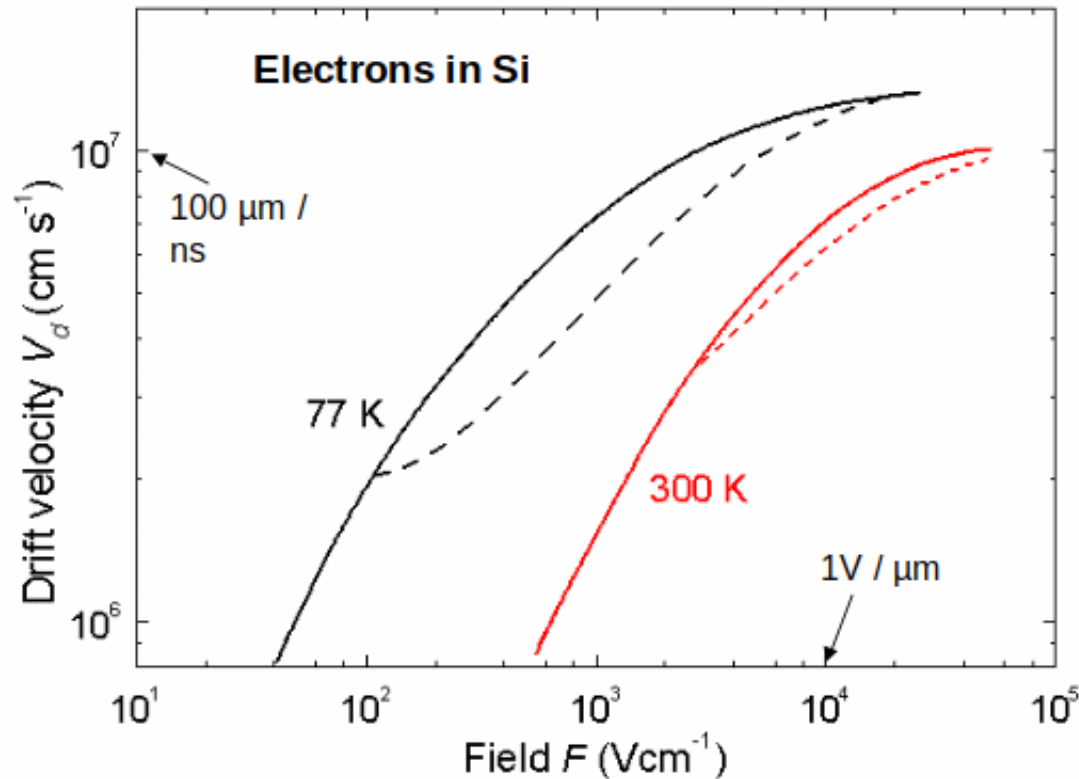
- > Absorption depth leads to time variation of signal pulse
- > Resulting time variation depends on both **absorption profile** and **carrier velocity**



Some comments on the time resolution

Time resolution in Si sensors

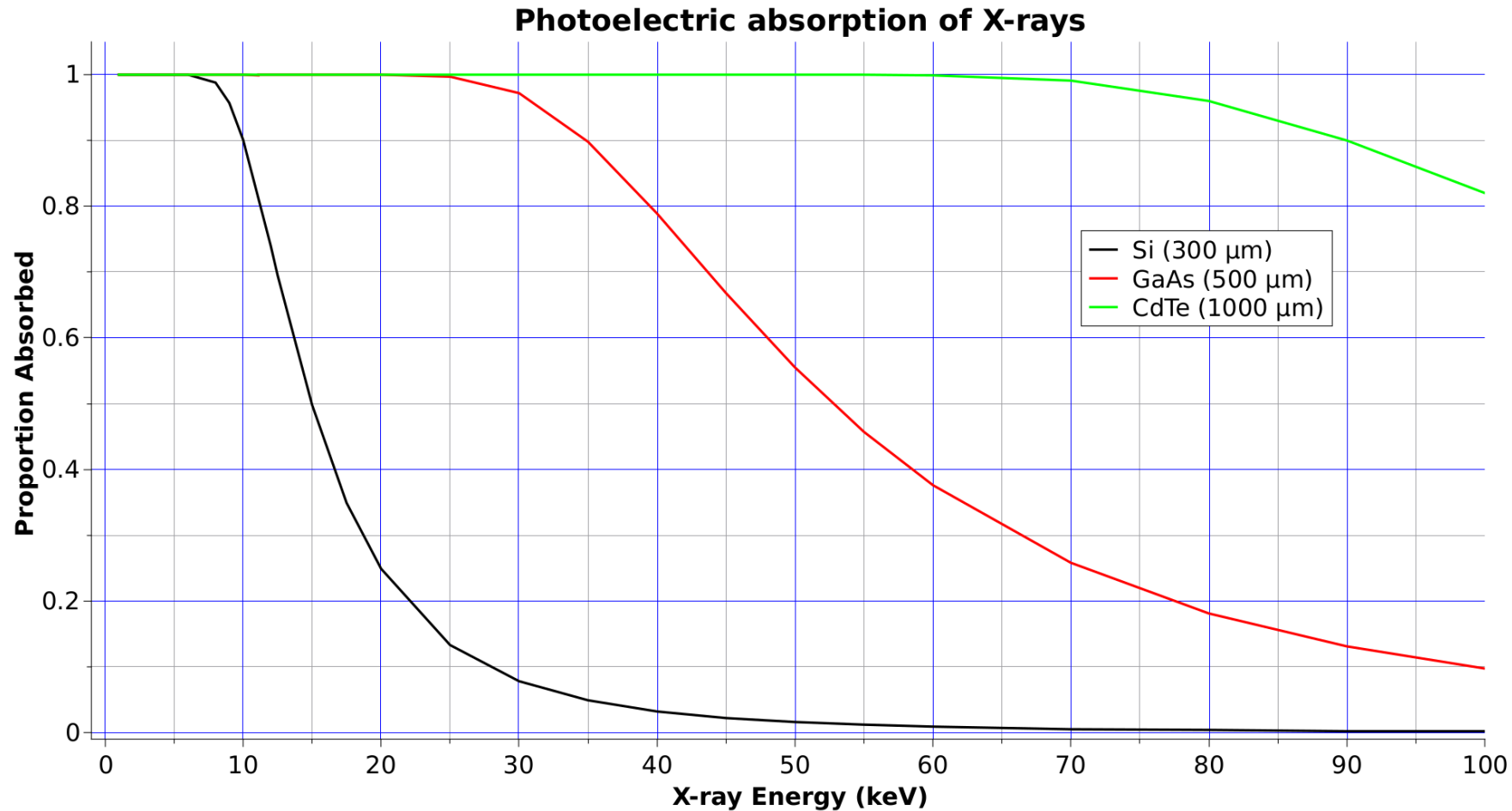
- **Drift velocity depends on carrier type** (electron or hole) and **field strength**
- Hole-collecting sensor, 300 μm thickness, 100 V bias -> **20 ns** max drift time
- Electron-collecting sensor, 300 μm thickness, 300 V bias -> **5 ns** max drift time (~ 1.5 ns RMS)



Some comments on the time resolution

High-Z materials

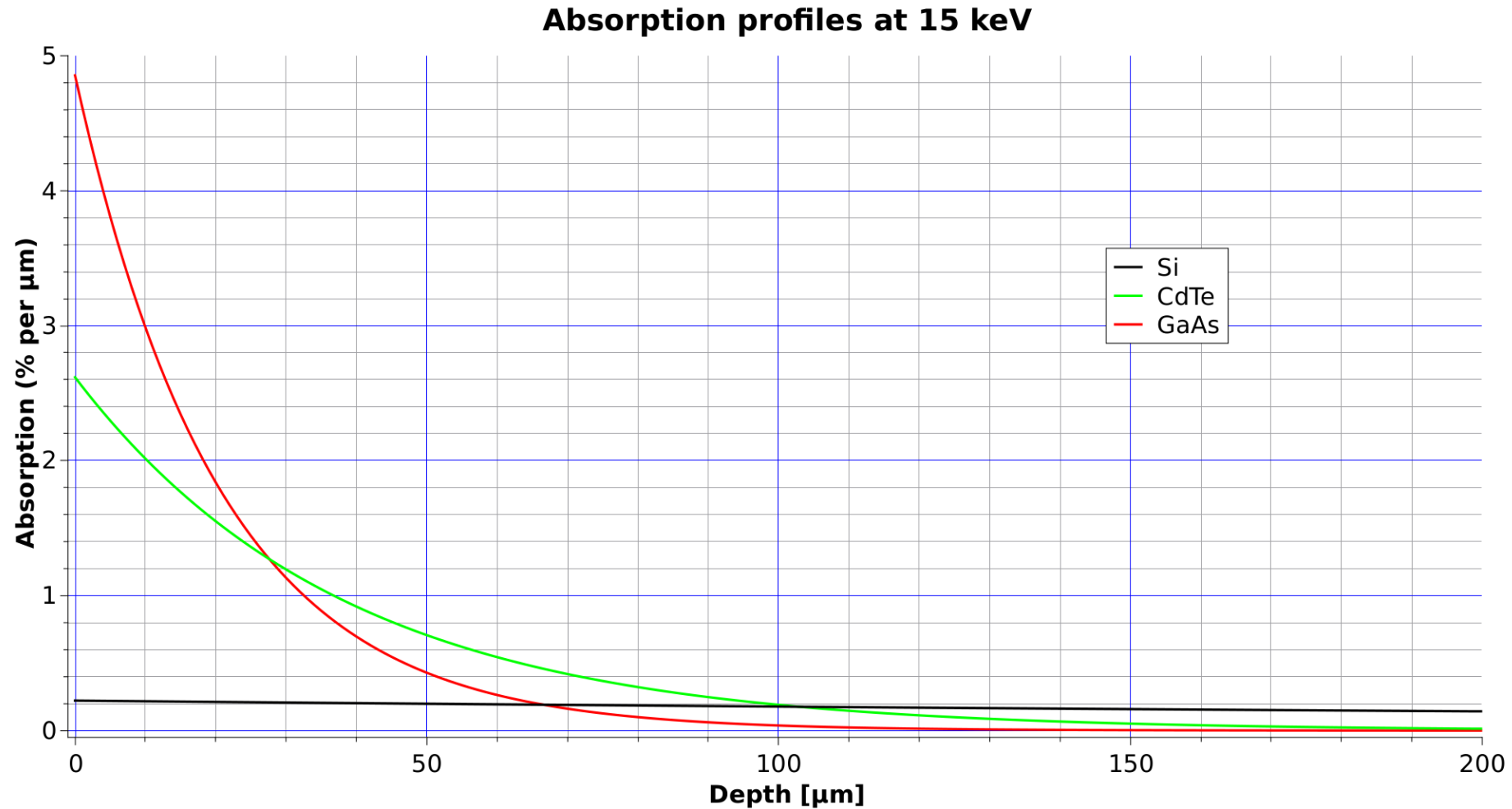
- > High-Z materials can offer more localized X-ray absorption, improving consistency of drift time



Some comments on the time resolution

High-Z materials

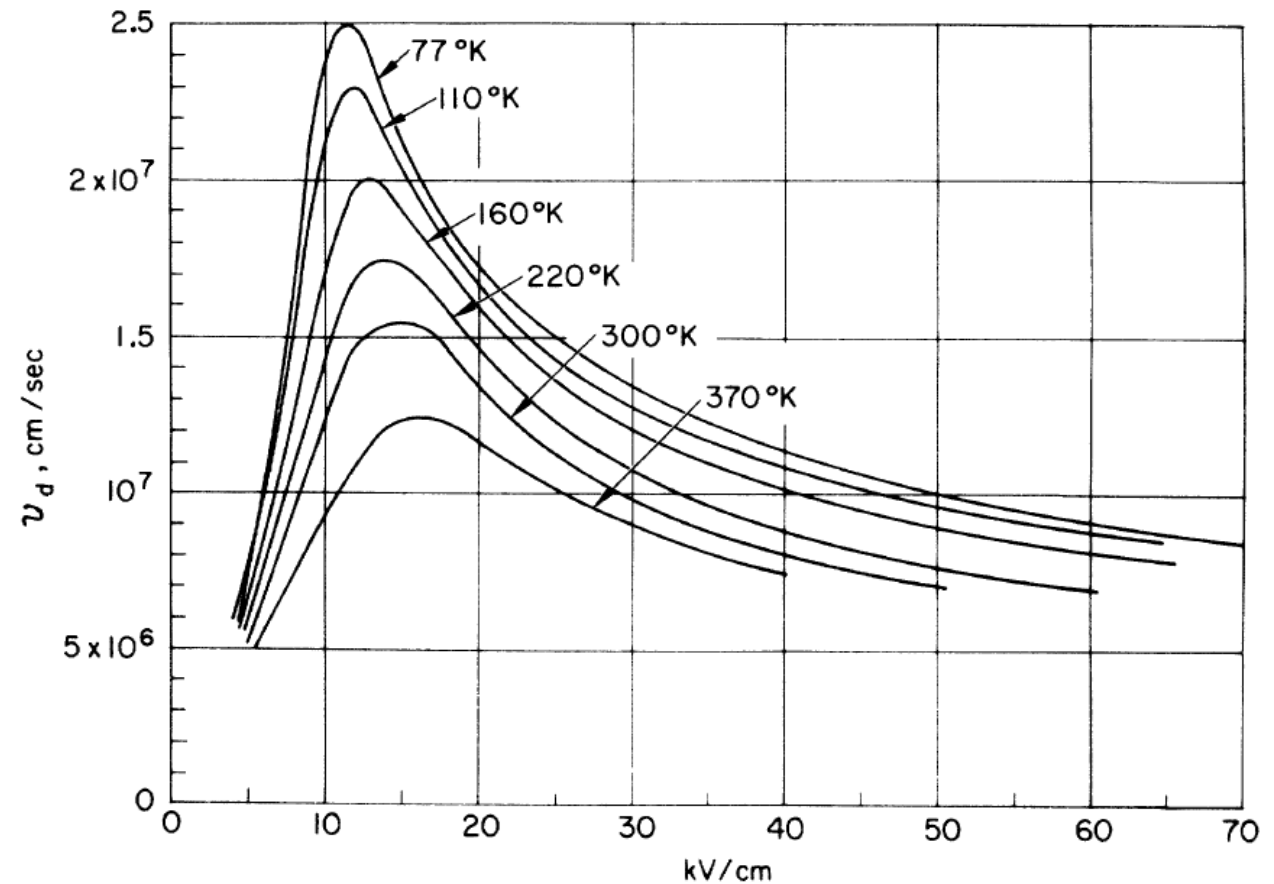
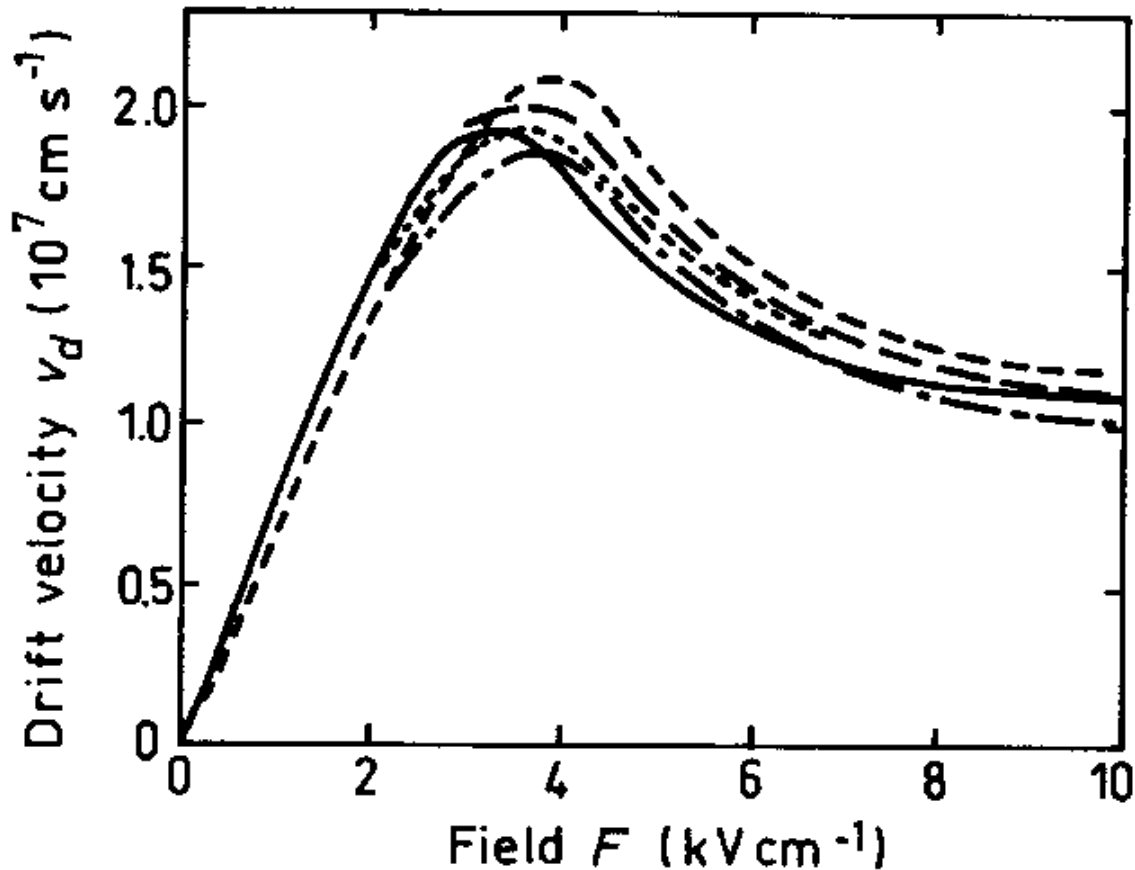
- > High-Z materials can offer more localized X-ray absorption, improving consistency of drift time



Some comments on the time resolution

Carrier mobility in high-Z semiconductors

- GaAs – high saturation velocity with “sweet spot” at ~ 4 kV/cm field (i.e. 200V with 500 μ m sensor)
- CdTe – comparable behaviour to electron-collecting Si, though high sensor thickness requires higher potential for given field strength (e.g. 500V bias for 5e6 cm/s velocity)



Some comments on the time resolution

Estimated drift time behaviour in different sensors

15 keV photons

	Si (h+), 300 μm , 100V	Si (e-), 300 μm , 300V	CdTe, 1000 μm , 500V	GaAs, 500 μm , 200V
RMS variation	2.86 ns	1,43 ns	0,76 ns	0,12 ns
Mean diff variation	2.46 ns	1,23 ns	0,56 ns	0,09 ns

17.5 keV photons

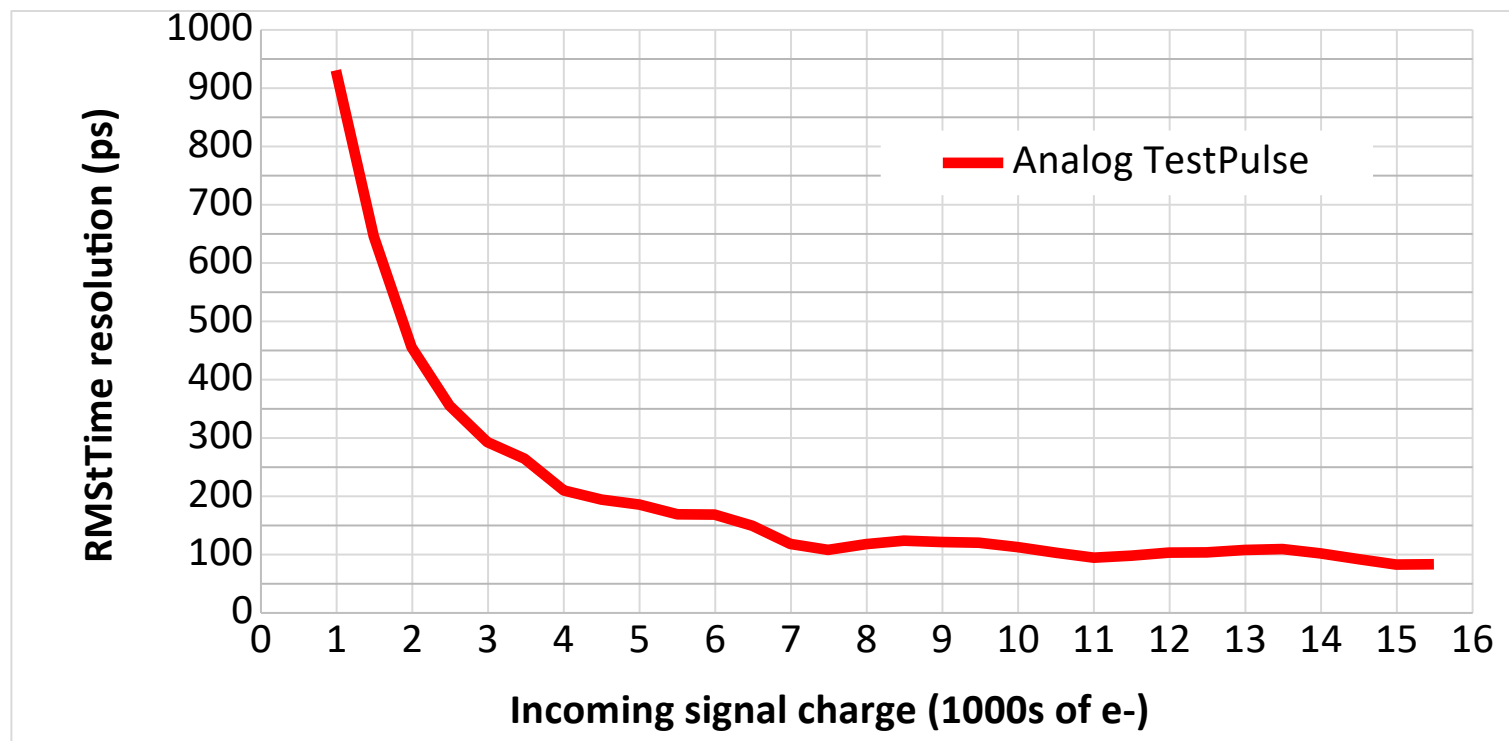
	Si (h+), 300 μm , 100V	Si (e-), 300 μm , 300V	CdTe, 1000 μm , 500V	GaAs, 500 μm , 200V
RMS variation	2.88 ns	1,44 ns	1,16 ns	0,18 ns
Mean diff variation	2.48 ns	1,24 n	0,85 ns	0,13 ns

Some comments on the time resolution

Effects of material on signal magnitude and time jitter

> Mean electron-hole pair generation energy varies between materials, affecting time jitter:

- Si – 3.6 eV per pair -> 4170 e at 15 keV -> 200 ps RMS jitter
- CdTe – 4.45 eV per pair -> 3370 e at 15 keV -> 275 ps RMS jitter
- GaAs – 4.2 eV per pair -> 3570 e at 15 keV -> 250 ps RMS jitter

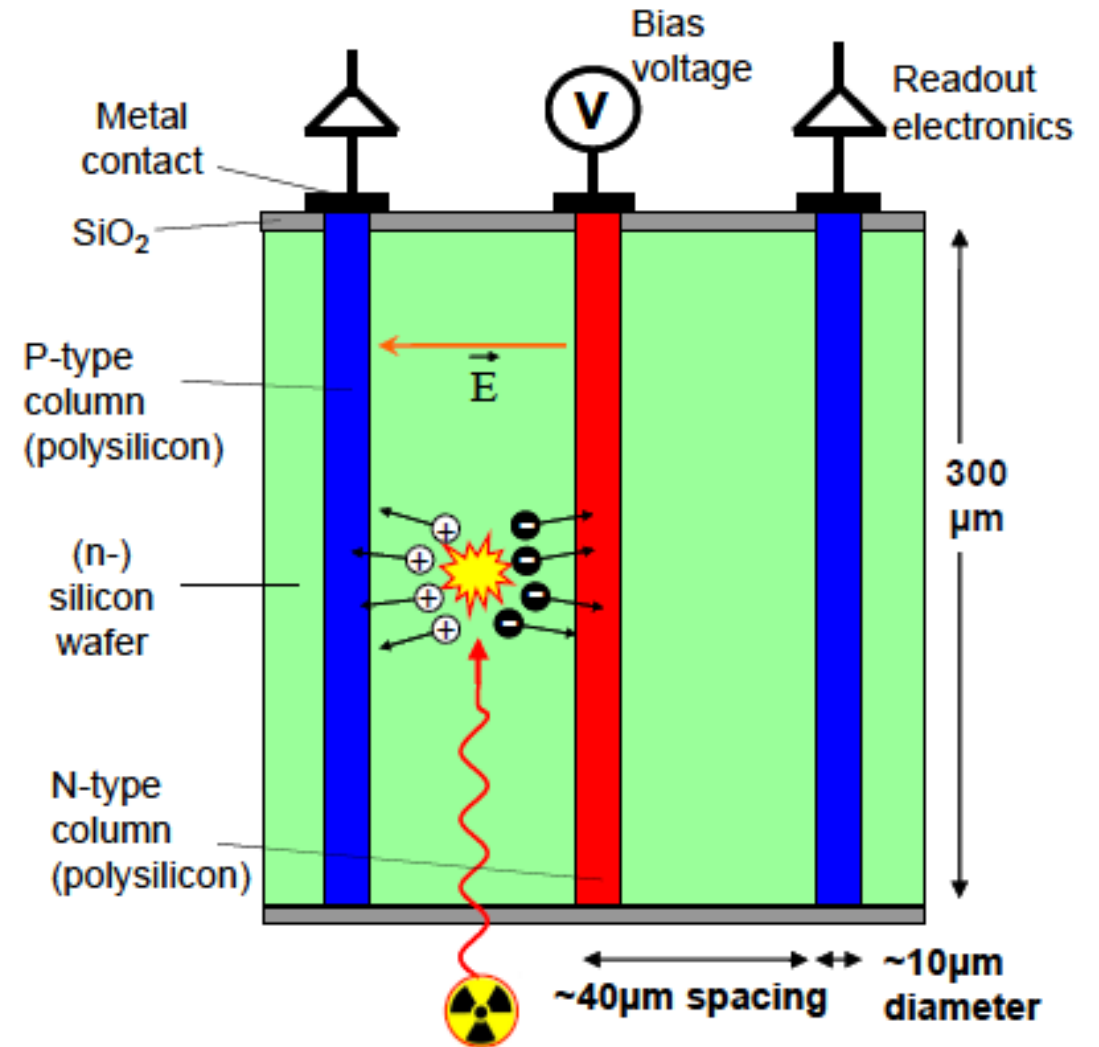


Time jitter would be main limiting factor for GaAs time resolution

Some comments on the time resolution

3D Silicon detectors

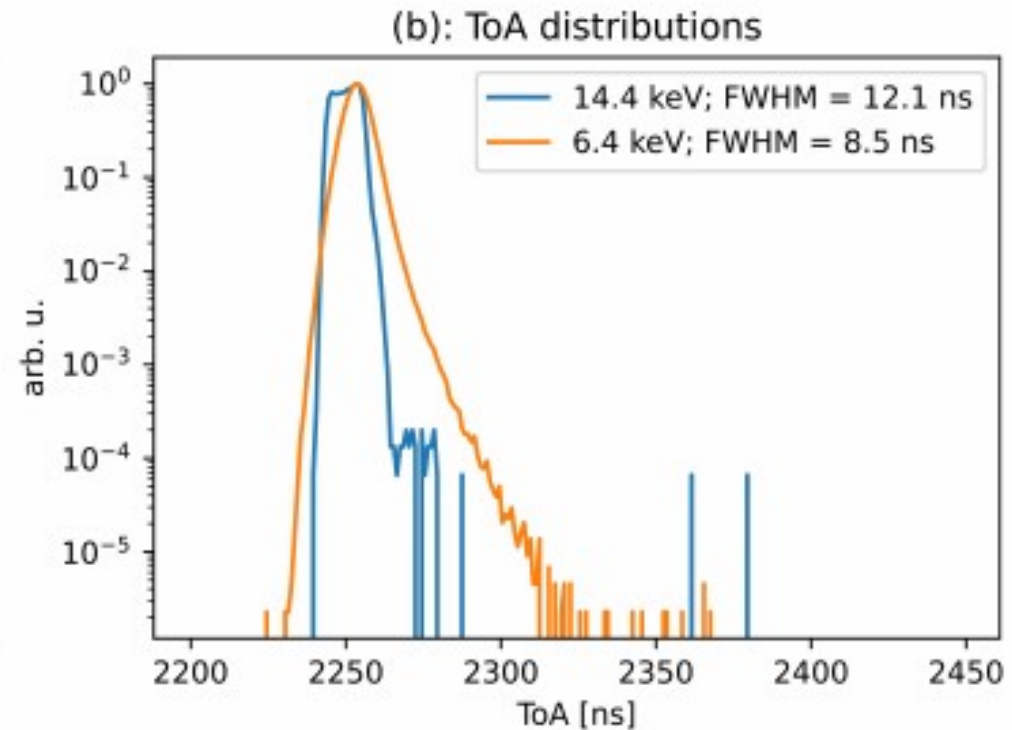
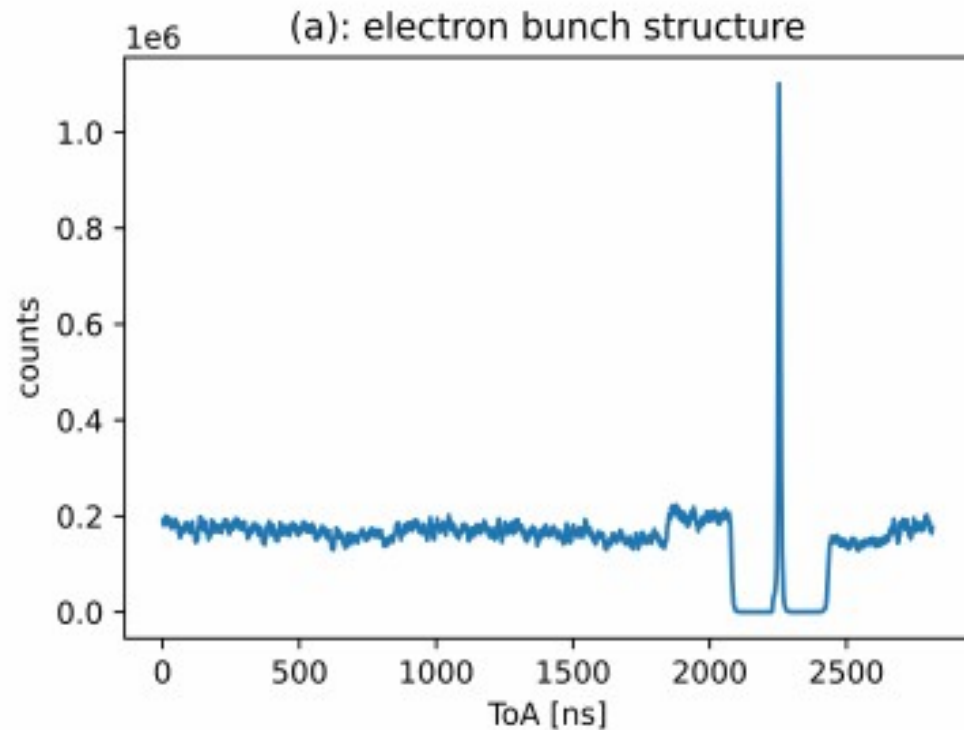
- > Electrode columns pass through Si substrate
 - Up to 300 μm thickness
 - $\sim 40\text{ }\mu\text{m}$ drift distance in Timepix4
 - Reduced charge sharing
- > Time resolution:
 - 0.8 ns max collection time ($\sim 0.25\text{ ns RMS}$)
 - Time jitter depends on energy
 - 0.25 RMS ns for 14.4 keV
- > Detectors already used at ATLAS



TEMPUS detector system first users beamtimes

First Experiments @ ESRF

- Campaign at ID14 in February on Nuclear Resonance Scattering
 - Improved sensor bias (300 μm , **200V**) and use of high-speed data links (1 x 1.28 Gbps)



Energy Calibration

Overview

Clustering

- Groups neighboring hits in space + time into single events
- Recovers energy from charge-sharing that would otherwise be split across pixels
- Produces cleaner ToT distributions with sharper peaks

ToT Analysis

- Construct histograms of clustered ToT values
- Peaks correspond to characteristic X-ray energies
- Gaussian fitting applied to determine peak positions
- Extracts precise ToT values that can be matched to known energies

Building Calibration Curve

- Collect ToT photopeak from different energies
- Build a relation $\text{ToT} \leftrightarrow \text{Energy}$
- Applied per pixel to correct response variations across the matrix
- Needed for improving time resolution (eg. Timewalk correction)

Clustering

Handling charge sharing

Charge Sharing

- Energy from one photon spreads into multiple neighboring pixels
- Clustering recombines these hits into a single physical event

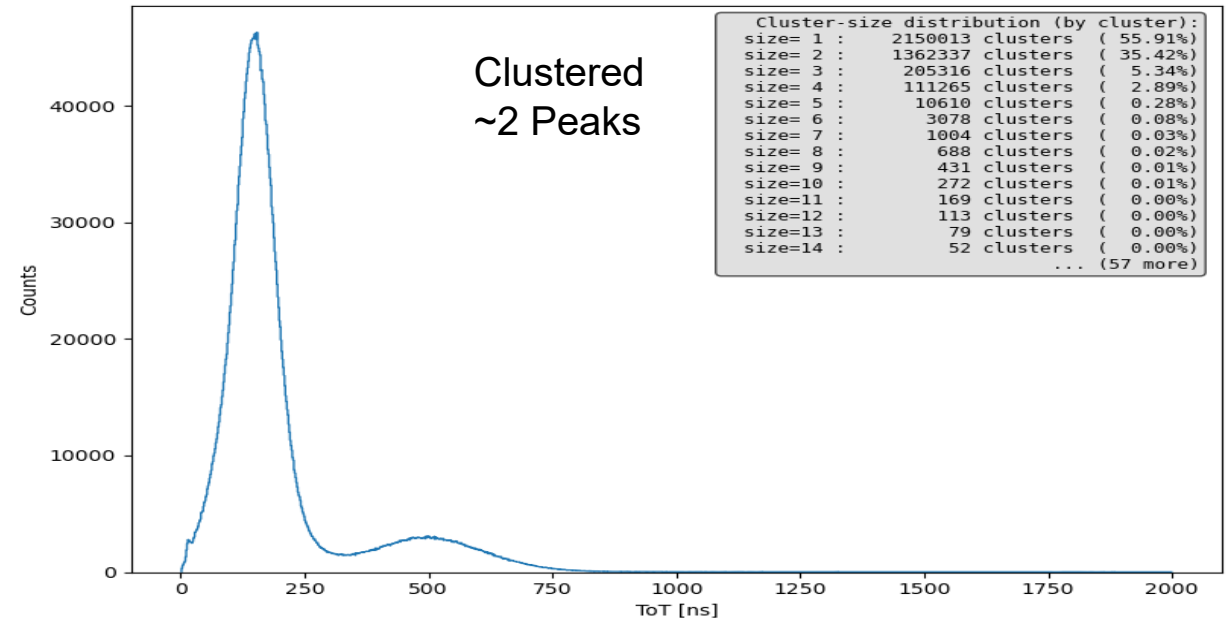
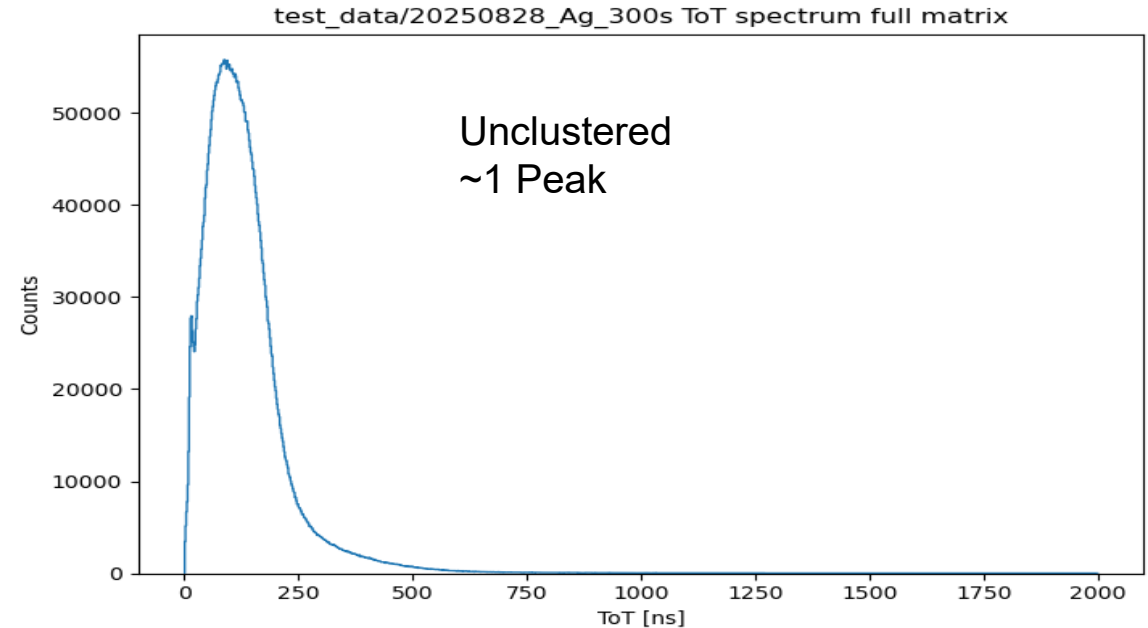
DBSCAN

- Density-based clustering: forms a cluster if points have enough neighbors within ϵ
- ϵ (eps): max separation to count as neighbors (units: px, ns/50)
- Distance in 3D (x, y, t') with scaled time:

$$d = ((\Delta x)^2 + (\Delta y)^2 + (\Delta \text{ToA} / \text{toa_scale})^2)^{1/2}$$

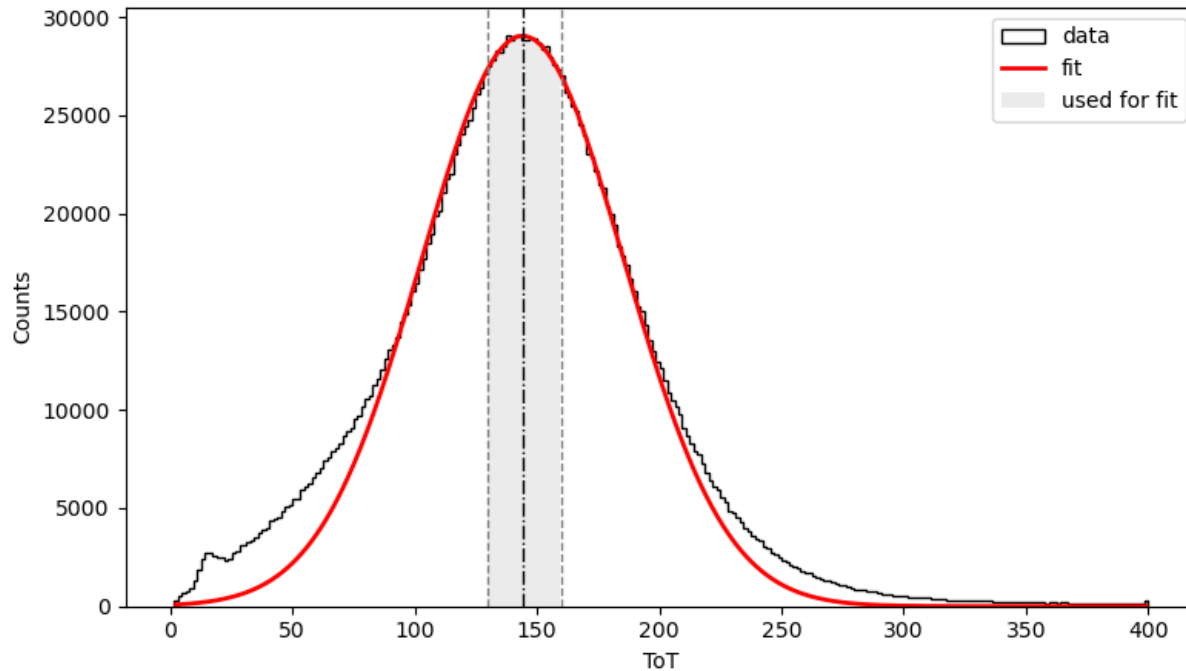
Handling Large Data Volume

- Enabled Parallelization inside DBSCAN
- Utilized built in ball tree algorithm to speed up neighbor queries
- Chunking by ToA to reduce memory/runtime



ToT Spectrum Analysis

Gaussian fit using manual window of [130.000, 160.000]
 $\mu=144.112\pm0.277$, $\sigma=41.427\pm1.491$



Fitting the photopeak

- Build clustered ToT histogram
- Select fit window around the peak (exclude tails/Covariant Peaks)
- Fit Gaussian

Seed parameters from full matrix

- Estimate global seeds from full-matrix spectrum:
 μ_0 = mode/centroid of global peak, σ_0 from FWHM
- Reuse these seeds for faster per-pixel fits

Iterate per pixel

- For each pixel with sufficient stats:
 - build histogram
 - apply same fit window
 - fit Gaussian
- Require $N_{\text{events}} \geq N_{\text{min}}$ (e.g., 300–500) to fit reliably
- Below threshold $\rightarrow$ skip/flag pixel

Store photopeak center

- Save μ (ToT_ns) per pixel for the corresponding energy for the data

Build Calibration Curve

Preliminary Findings

- Collect calibration points by repeating ToT analysis at multiple known photon energies.
- Parametric calibration function used in Timepix:
$$ToT(E) = aE + b - c / (E - t)$$
 - a linear slope term (how ToT grows with energy)
 - b offset (baseline shift)
 - c curvature term (corrects non-linearity, especially at low energy)
 - t effective threshold parameter (shifts the curve near threshold)
- In practice:
 - At higher energies, the relation is almost linear (dominated by a and b).
 - At lower energies, c and t adjust for threshold effects and front-end non-linearities
- Calibration done pixel-by-pixel to correct variations across the 512×448 matrix.
- Test pulse data is needed to fully determine the calibration curve, especially the low-energy part.

